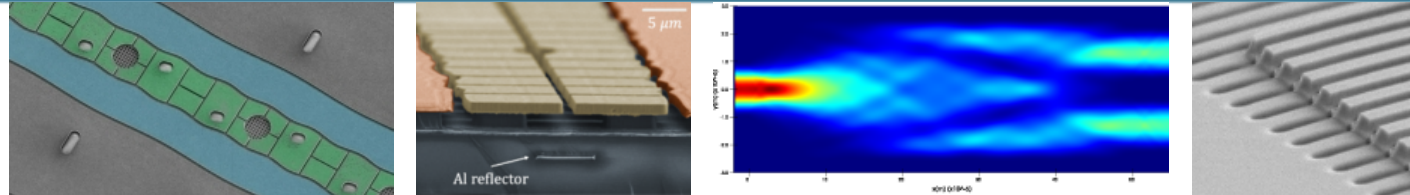
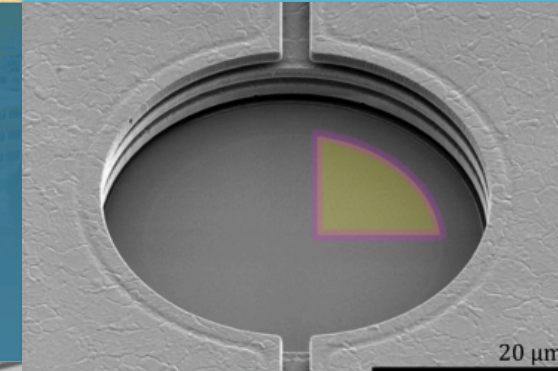




Integrated Photonics for Trapped Ion Quantum Information Experiments at Sandia Labs

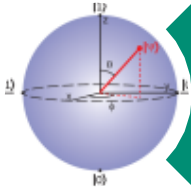


Hayden McGuinness, Michael Gehl, Will Setzer,
Nick Karl, Joon Kwon, Craig Hogle, Dan Stick

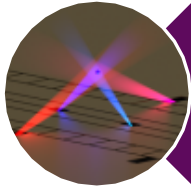
Quantum Nanophotonic Materials, Devices, and Systems
San Diego
August 23, 2022



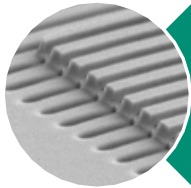
Sandia National Laboratories is a multimission laboratory managed and operated by National Technology & Engineering Solutions of Sandia, LLC, a wholly owned subsidiary of Honeywell International Inc., for the U.S. Department of Energy's National Nuclear Security Administration under contract DE-NA0003525.



Brief intro to trapped ions for QIP



Ion projects employing integrated photonics



Waveguides, gratings, and more



Single-Photon Avalanche Diode

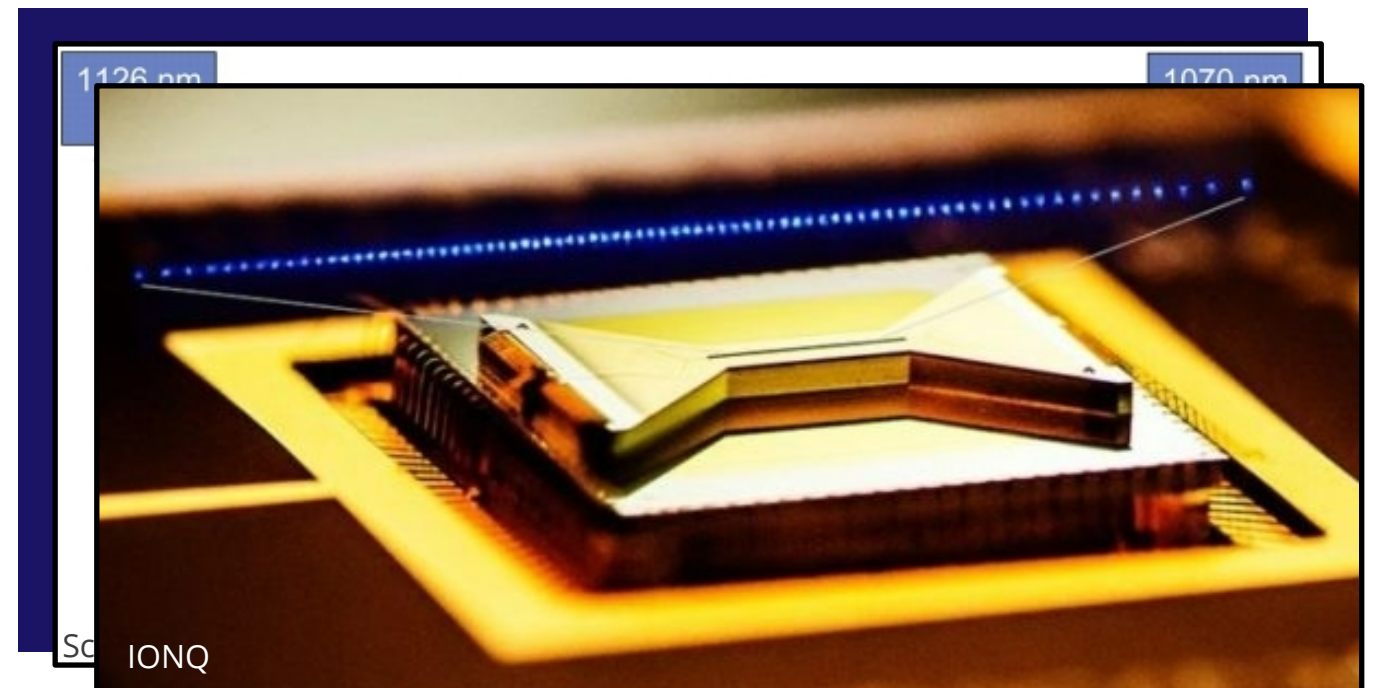
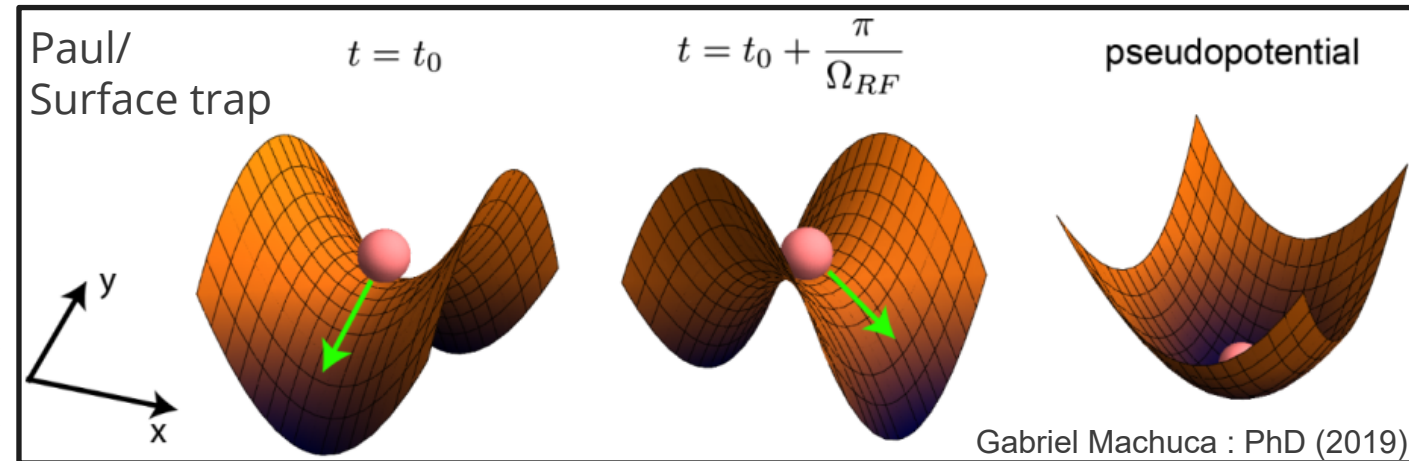


Optical Modulators

Trapped Ions for Quantum Information and Sensing



- What is a trapped ion?
 - Neutral atom/molecule stripped of $1+ e^-$
 - Confined with RF/DC, E/M potentials

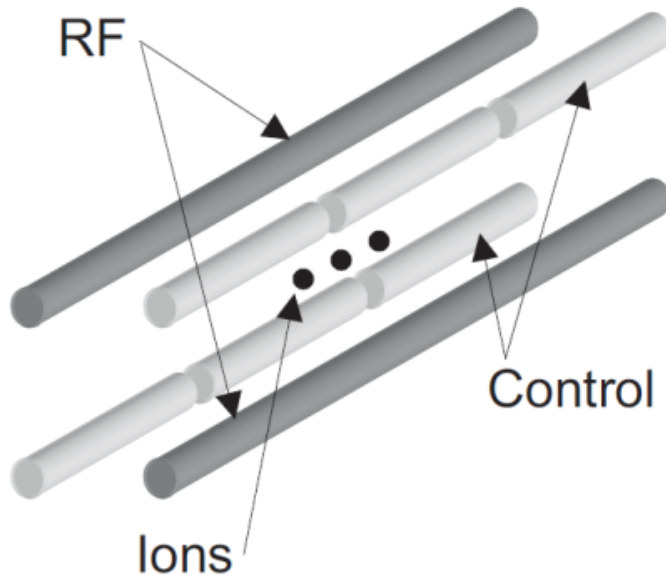


Pros	Cons
Identical qubits*	Slow operation (MHz)
Best fidelities	Multiple lasers
Can be fully connected	Ion loss
Scalability?	Scalability?

- Application
 - Fundamental Physics
 - Sensors (**Clocks**, inertial, EM)
 - **Computation**

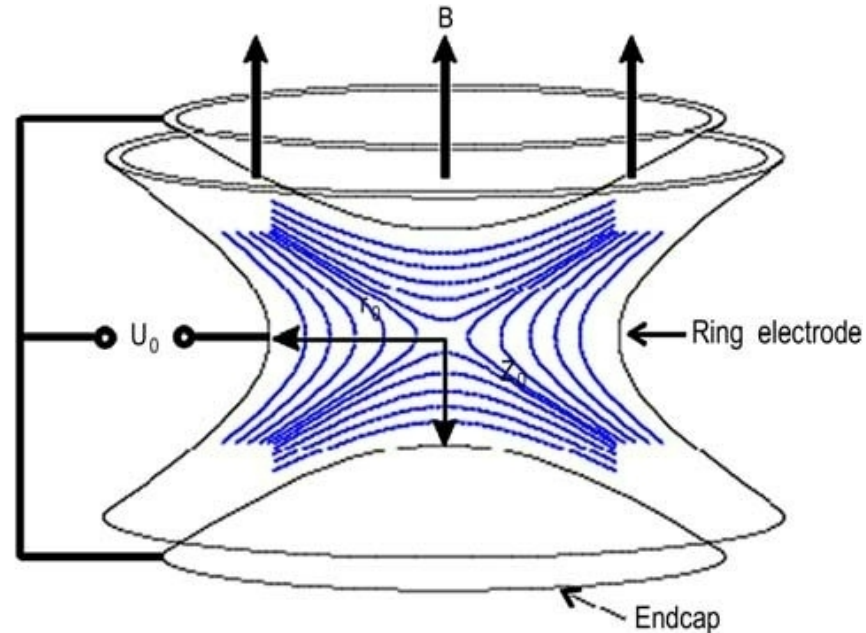
*In identical environments

Paul Trap



- Static and dynamic electric fields
- Simple
- Deep trap depth
- Difficult to Scale

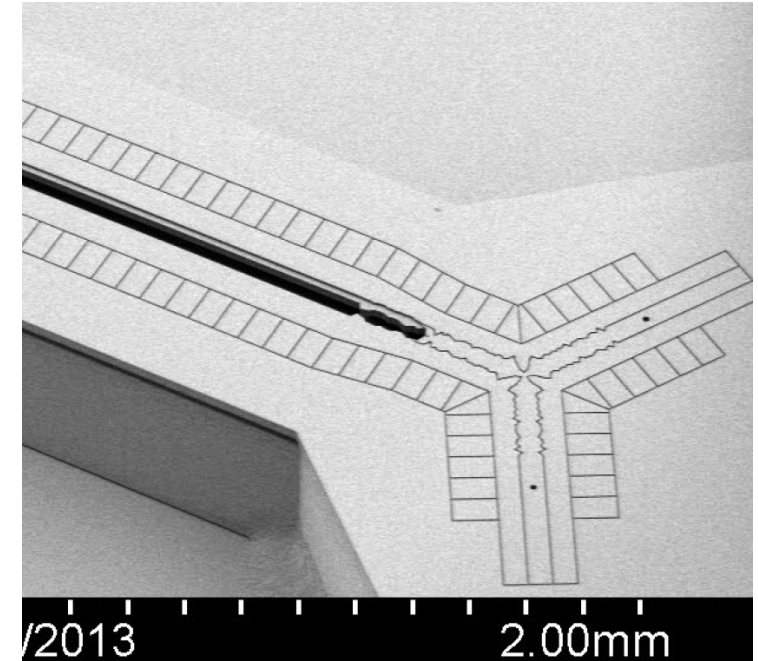
Penning Trap



Plasma Science and Technology **11**, 5, 521 (2009)

- Static electric and magnetic fields
- Simple
- Deep trap depth
- Difficult to Scale

Surface Trap

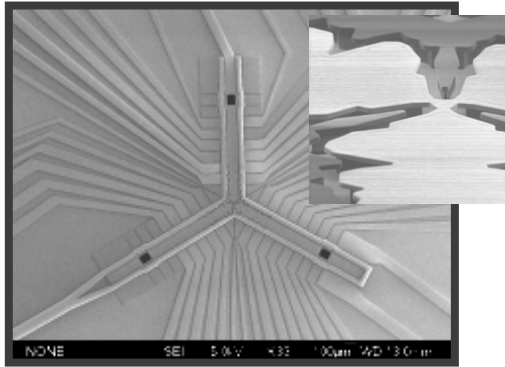


- Static/dynamic E-fields
- Manufacturable, repeatable
- Integrate technologies
- Difficult to make
- Lower trap depth
- Scalable

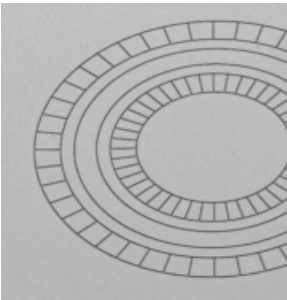
Some of Sandia's Surface Traps



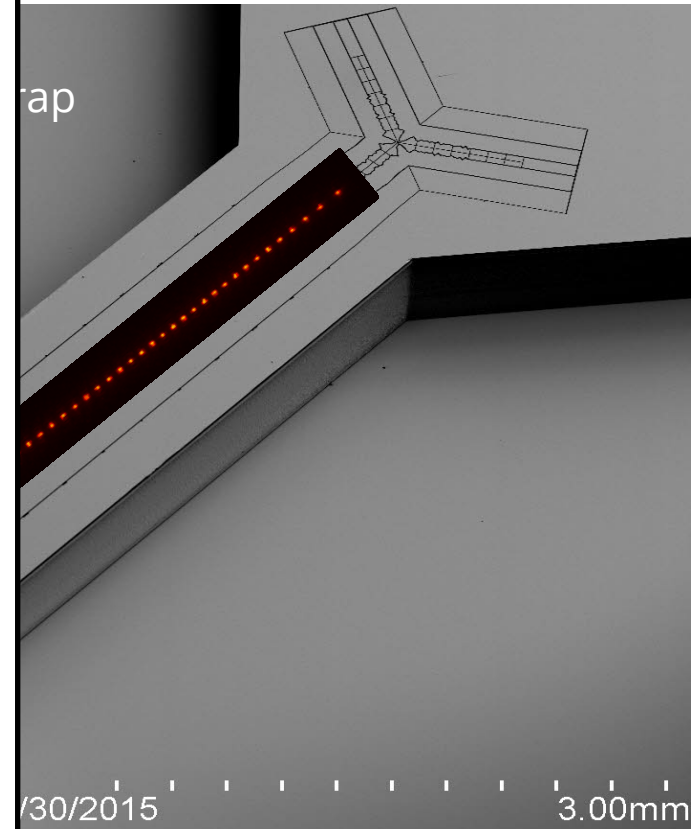
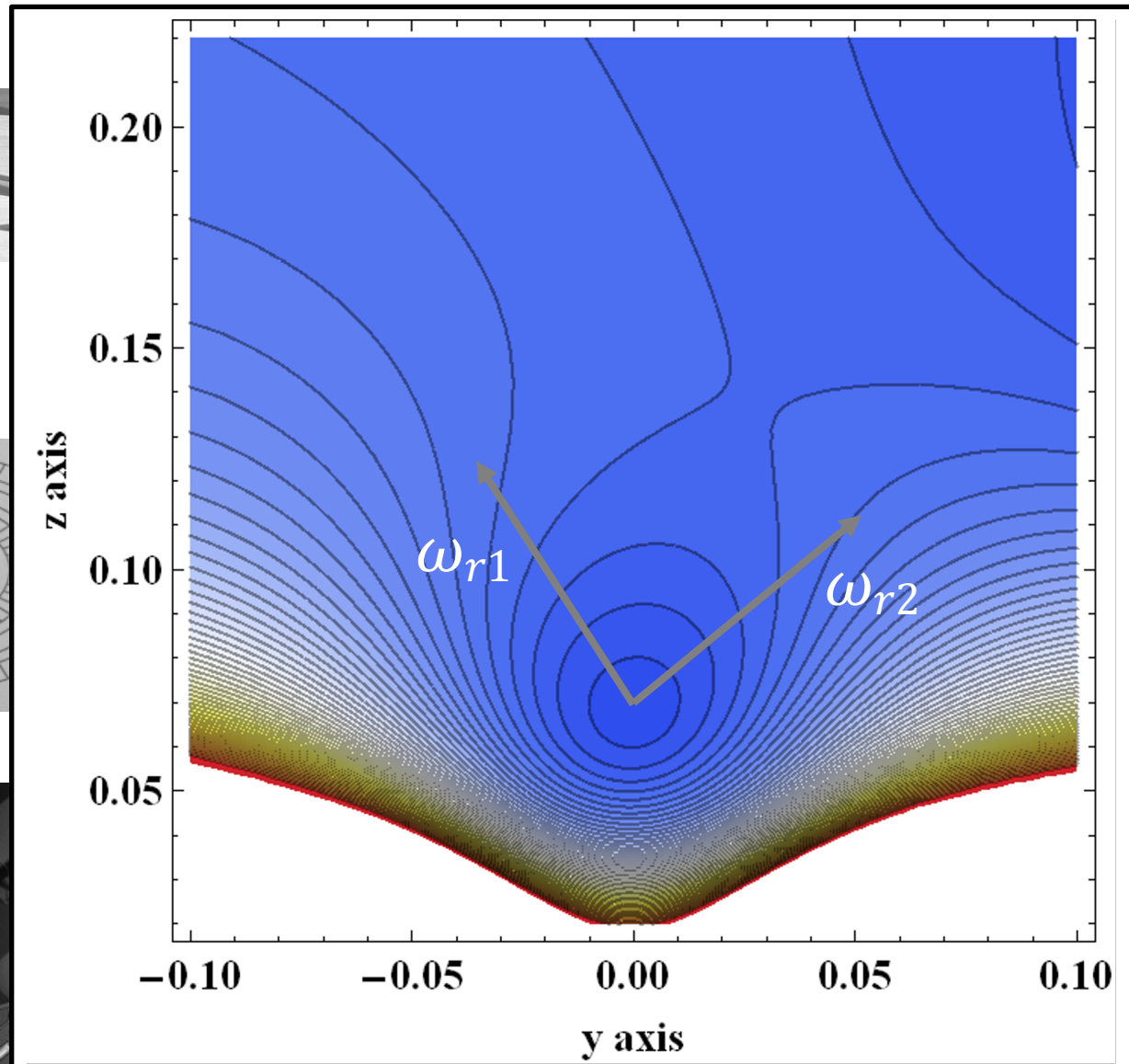
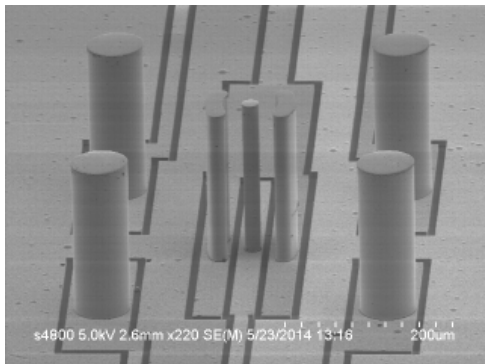
Y-junction traps



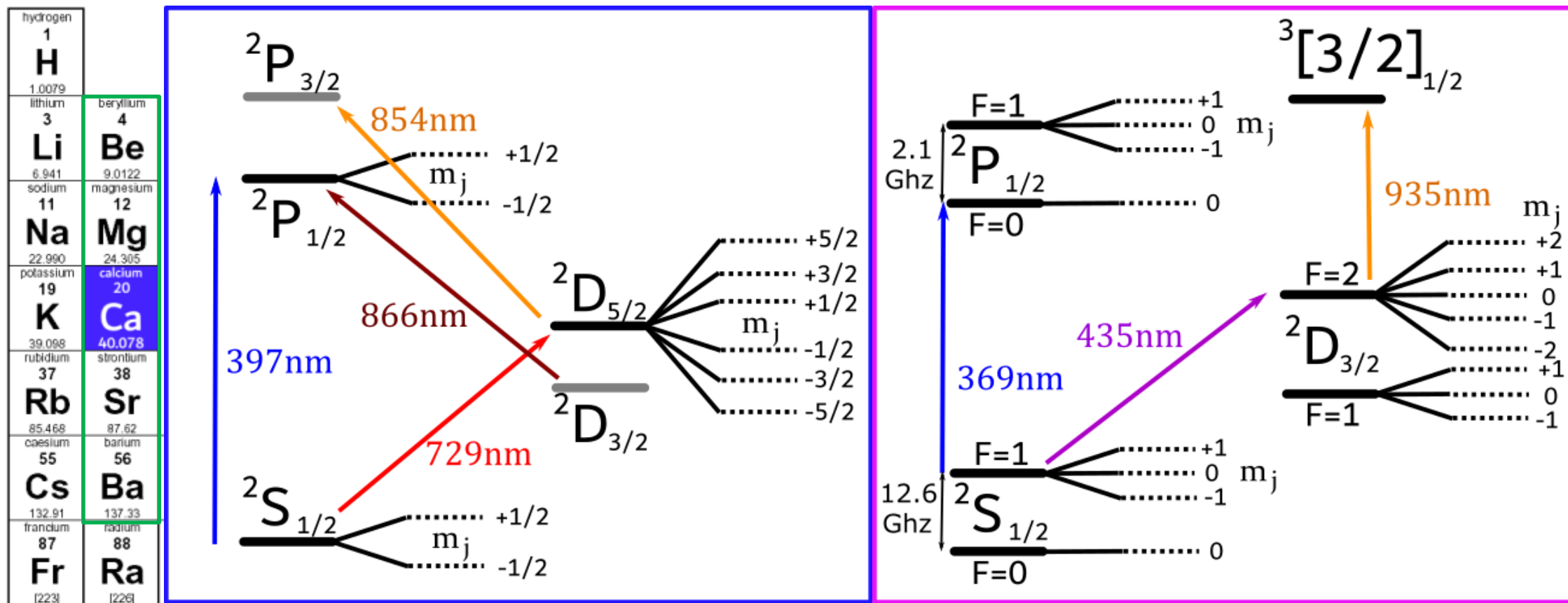
Ring trap:



Stylus trap



Two Common Ion Species: $^{171}\text{Yb}^+$ and $^{40}\text{Ca}^+$

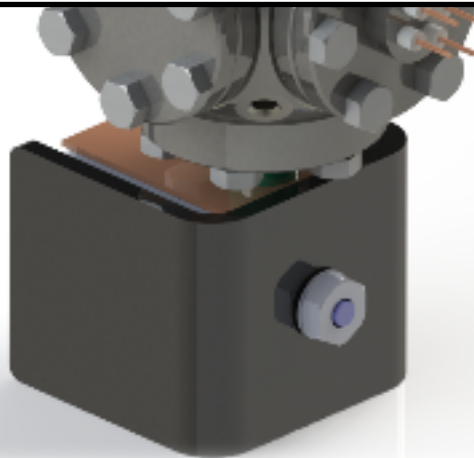
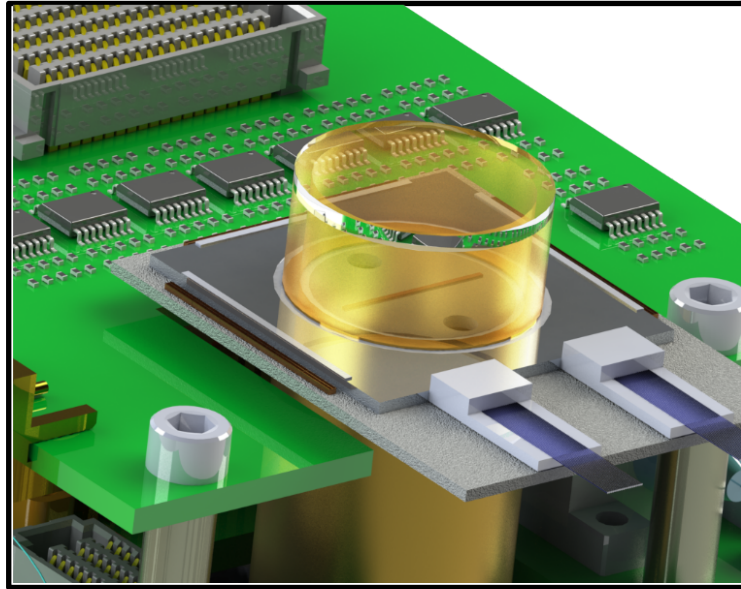


* Lanthanide series

** Actinide series

lanthanum 57 La 138.91 [227]	cerium 58 Ce 140.12	praseodymium 59 Pr 140.91 [231.04]	neodymium 60 Nd 144.24 [238.03]	promethium 61 Pm [145]	samarium 62 Sm 150.36 [244]	europium 63 Eu 151.96 [243]	gadolinium 64 Gd 157.25 [247]	terbium 65 Tb 158.93 [247]	dysprosium 66 Dy 162.50 [251]	holmium 67 Ho 164.93 [252]	erbium 68 Er 167.26 [257]	thulium 69 Tm 168.93 [258]	ytterbium 70 Yb 173.04 [259]
actinium 89 Ac [227]	thorium 90 Th 232.04	protactinium 91 Pa 231.04	uranium 92 U 238.03	neptunium 93 Np [237]	plutonium 94 Pu [244]	americium 95 Am [243]	curium 96 Cm [247]	berkelium 97 Bk [247]	californium 98 Cf [251]	einsteinium 99 Es [252]	fermium 100 Fm [257]	mendelevium 101 Md [258]	nobelium 102 No [259]

Trapped Ion Clock with photonic Technologies on Chip (TICTOC)



Solder-bonding
vacuum cell

200+ thru-vacuum
electrical and optical I/O
delivered via PIC

Doubler system

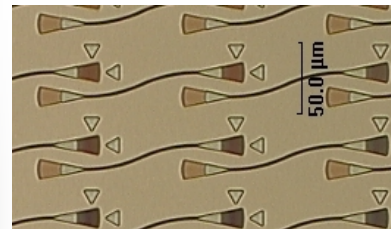
Comb system

435 nm laser +
WGM resonator

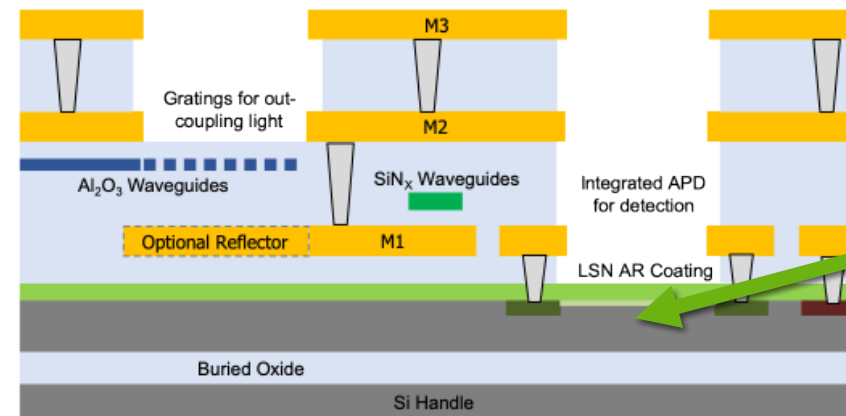
369 nm, 399 nm,
760 nm, 935 nm
fiber array input

Cross section of Ion trap

Detection:
Avalanche
photodiodes

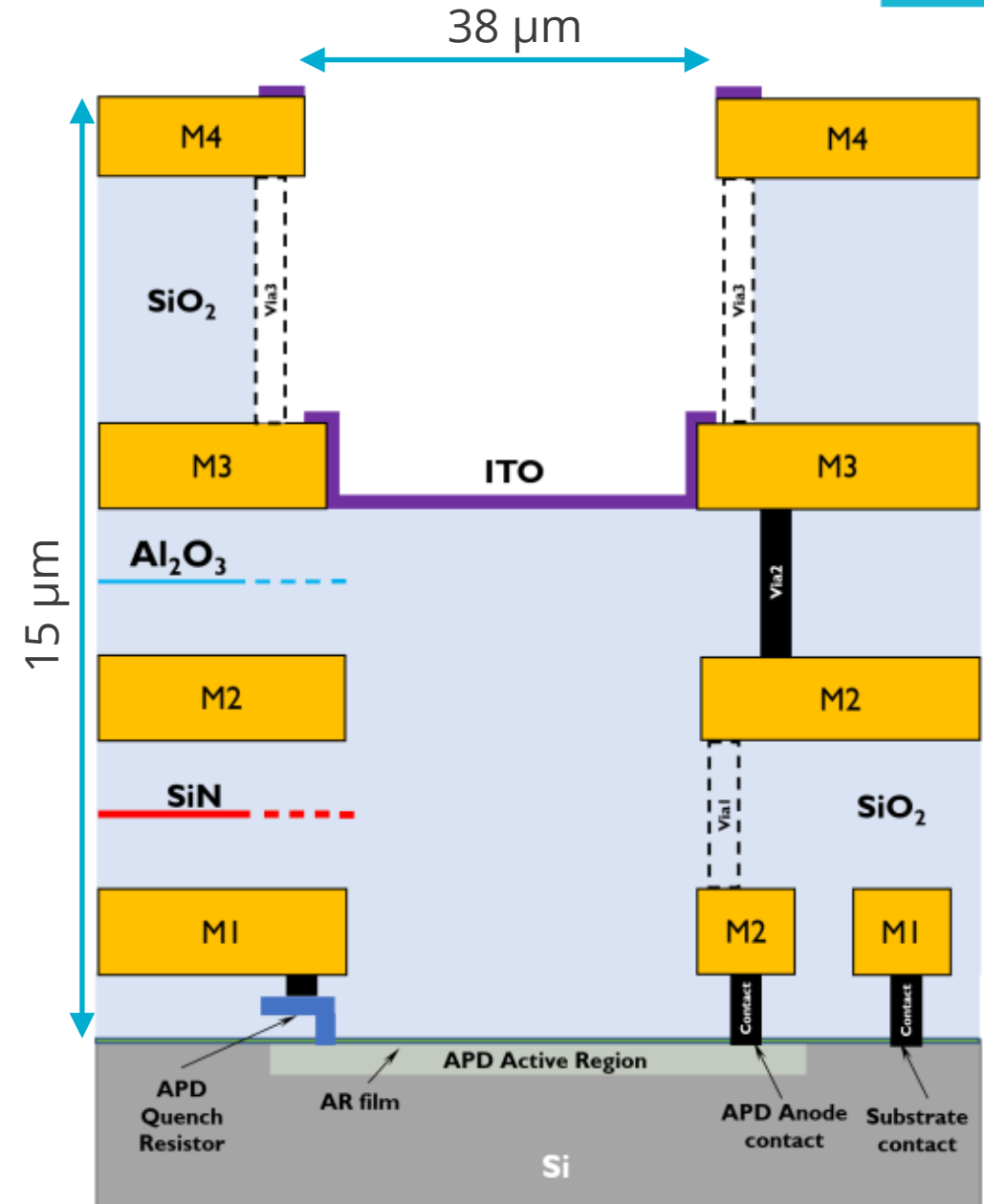
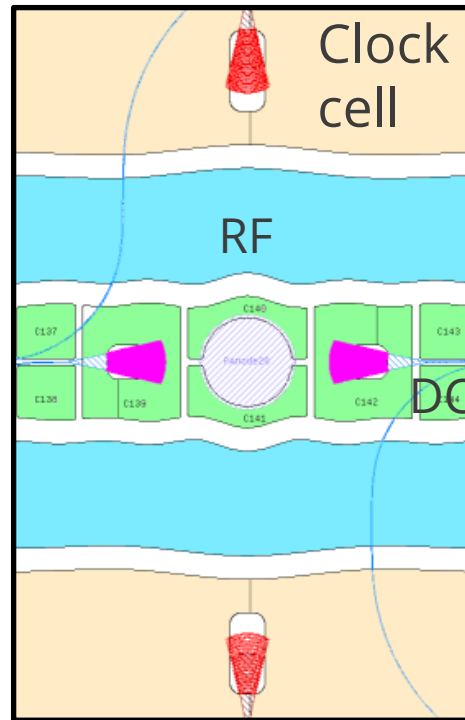
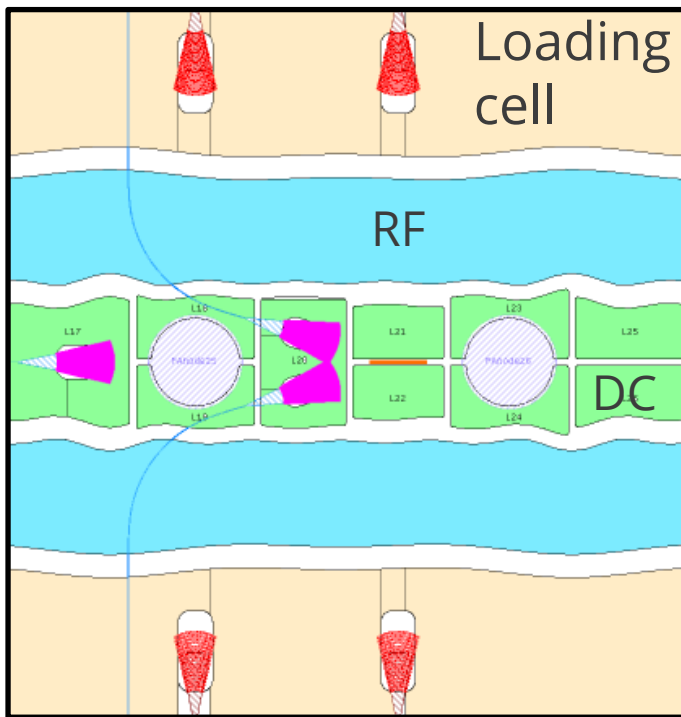


Light delivery with
waveguides and
grating couplers



TICTOC 2

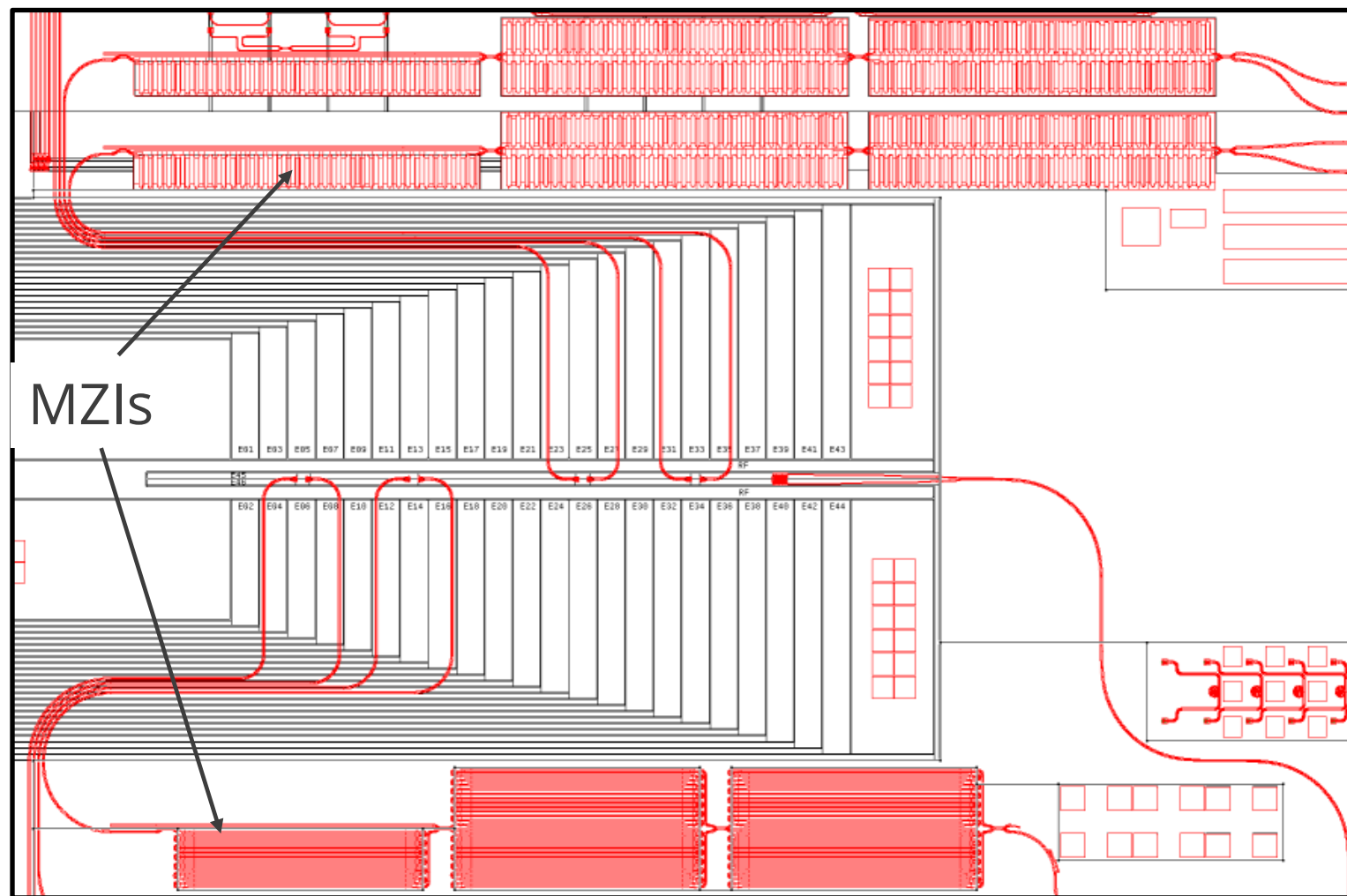
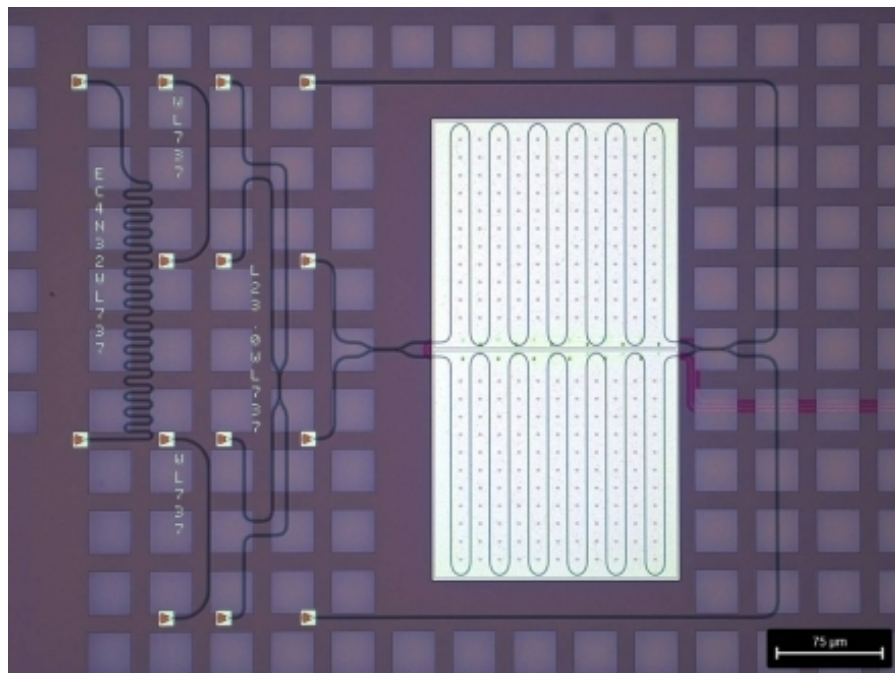
- Final TICTOC trap out of fab soon, $^{171}\text{Yb}^+$
 - 2 types of cells: “Clock” and “Load”
 - 369, 399, 435, 760, 935 nm light
 - Optimized electrode design, 50 μm height
 - Focusing output gratings, $\sim 4 \mu\text{m}$ UV spot size
 - Loading sites also storage



Modulators + Gratings : Malpais



- $^{40}\text{Ca}^+$, modulators + gratings
 - Multiple MZI designs
 - Edge coupled (off screen)
 - Designed for 729 nm
 - High fidelity 1 and 2-qubit gates





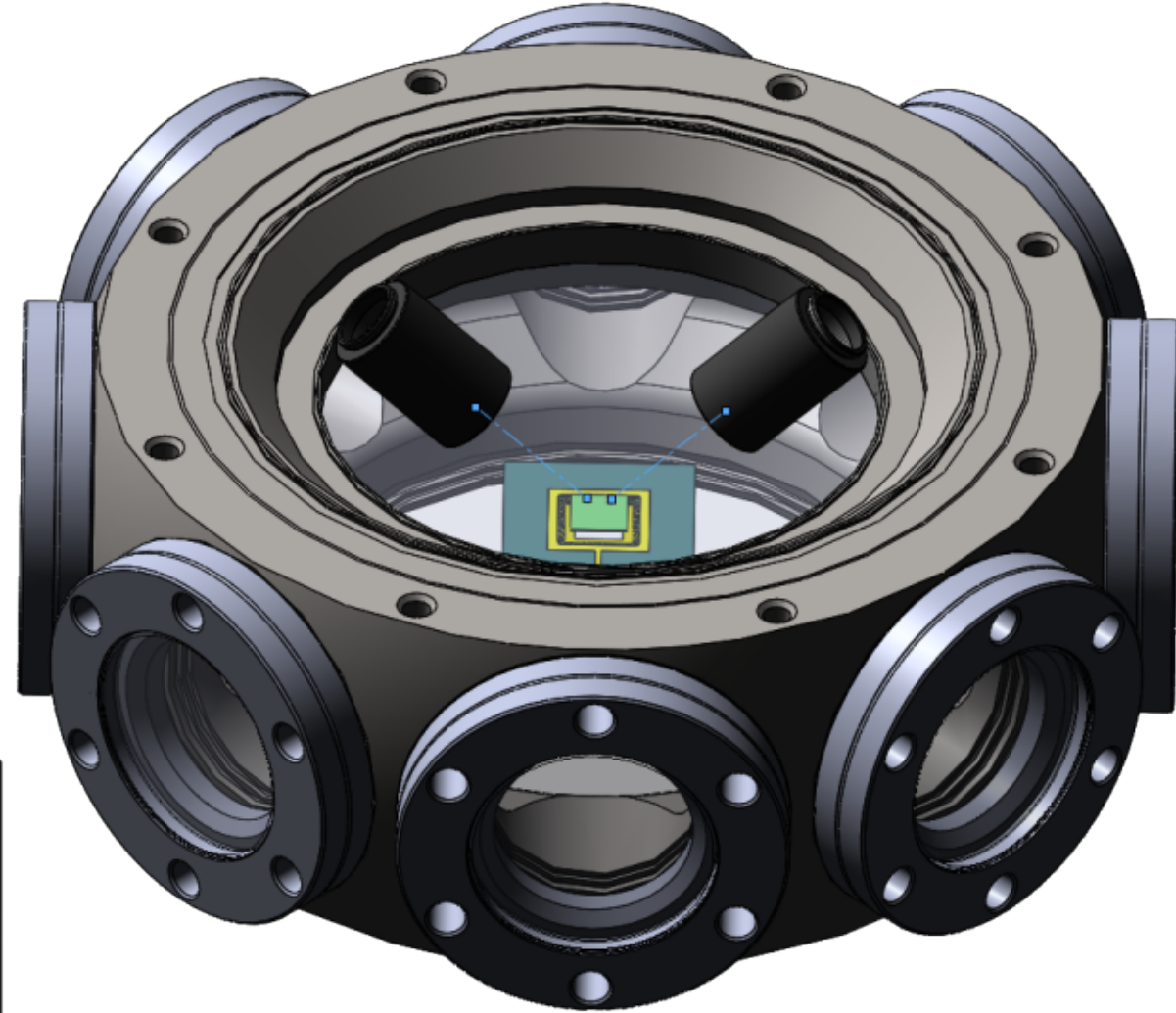
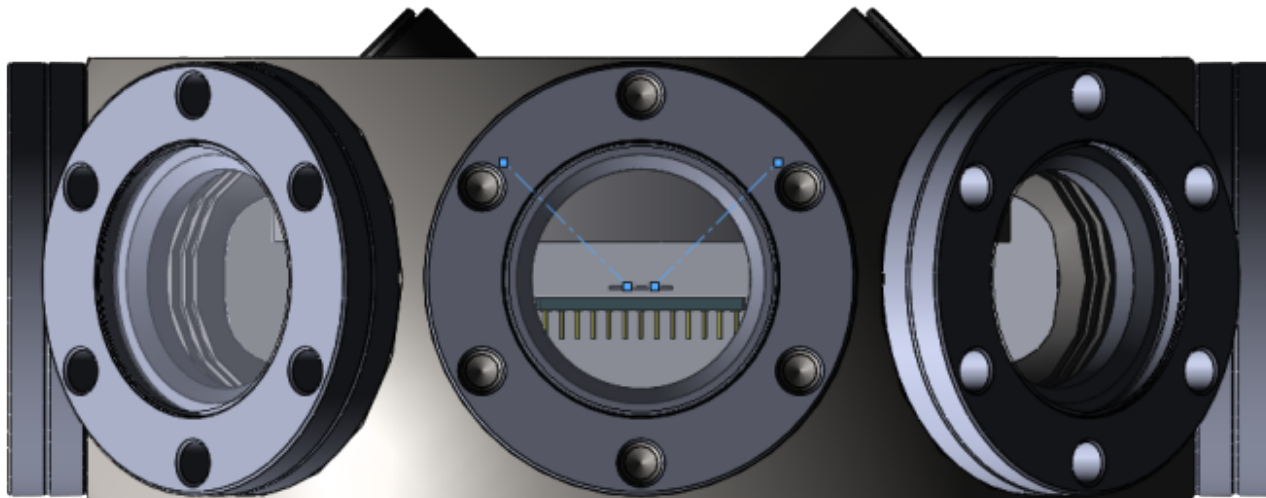
Waveguides, Gratings, and More



Waveguides and Gratings: Coupling In



- Requires coupling through vacuum chamber
 - $\sim 1\text{E-}11$ Torr, UHV
 - Room temperature/Cryo
- Mostly top-down grating couple (edge optional)
 - Fiber attach in the works



Waveguides and Gratings: Coupling In 2



Input for $^{171}\text{Yb}^+$:

369 nm: "Doppler" cooling

399 nm: Neutral atoms \rightarrow strip electron = ion

435 nm: Clock/qubit

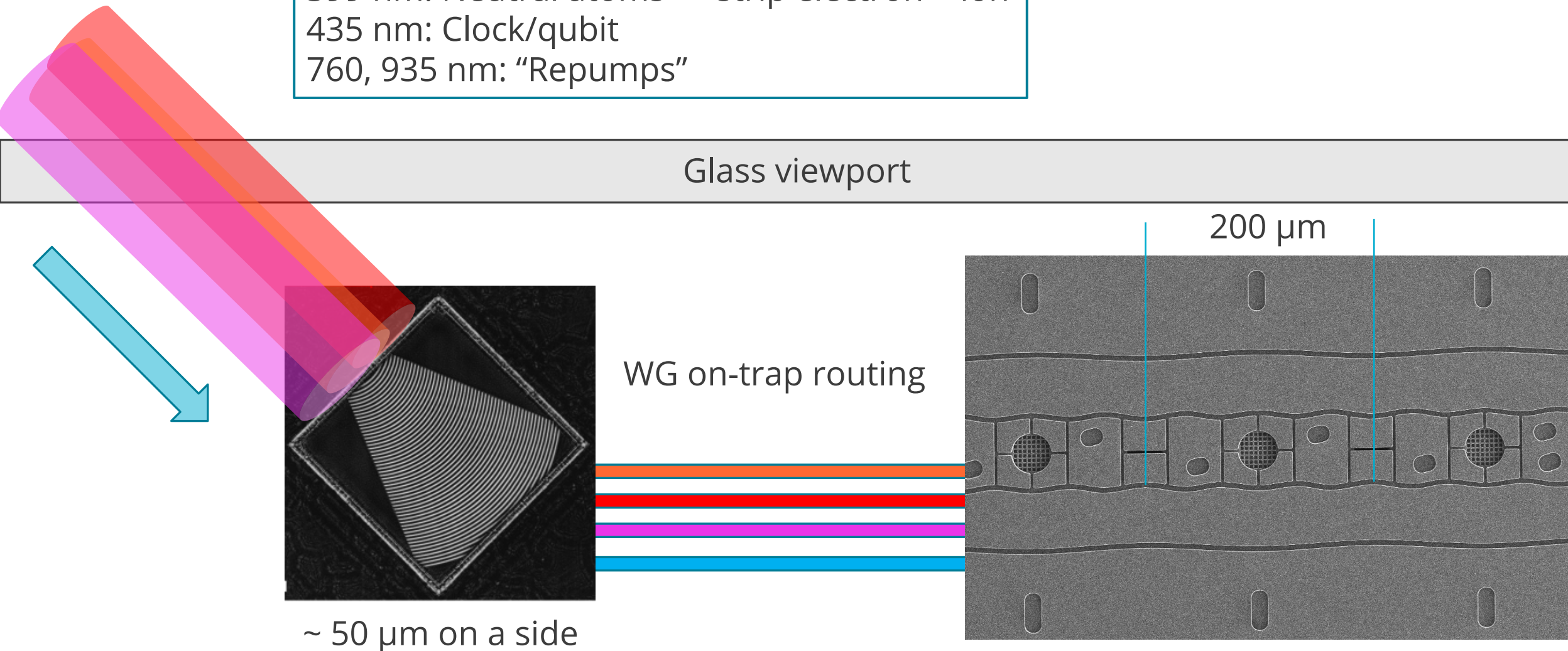
760, 935 nm: "Repumps"

Glass viewport

WG on-trap routing

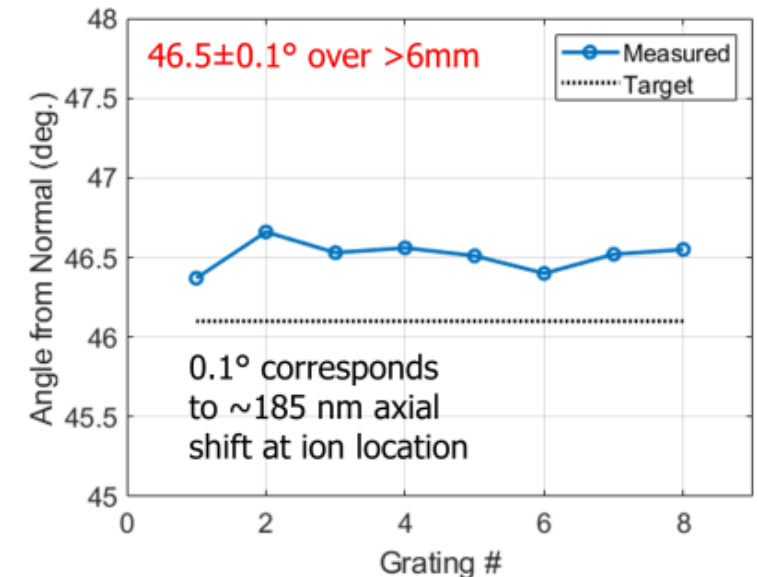
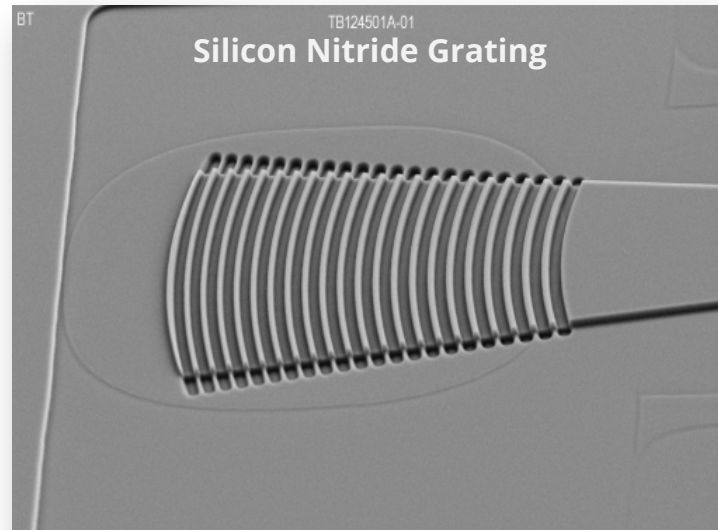
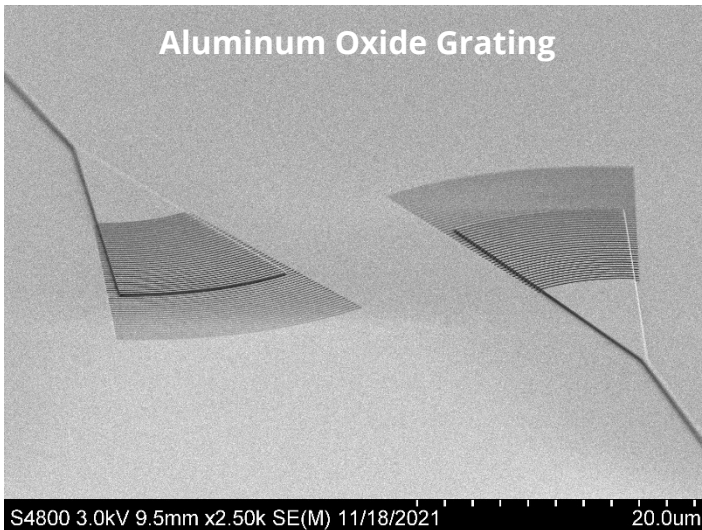
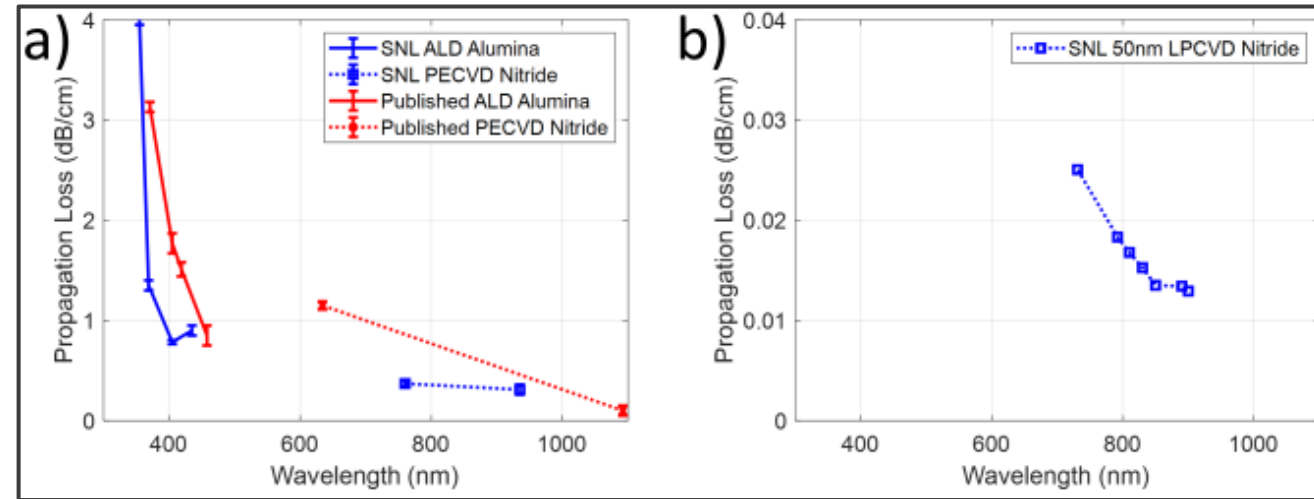
200 μm

$\sim 50 \mu\text{m}$ on a side



Waveguides and Gratings: Materials

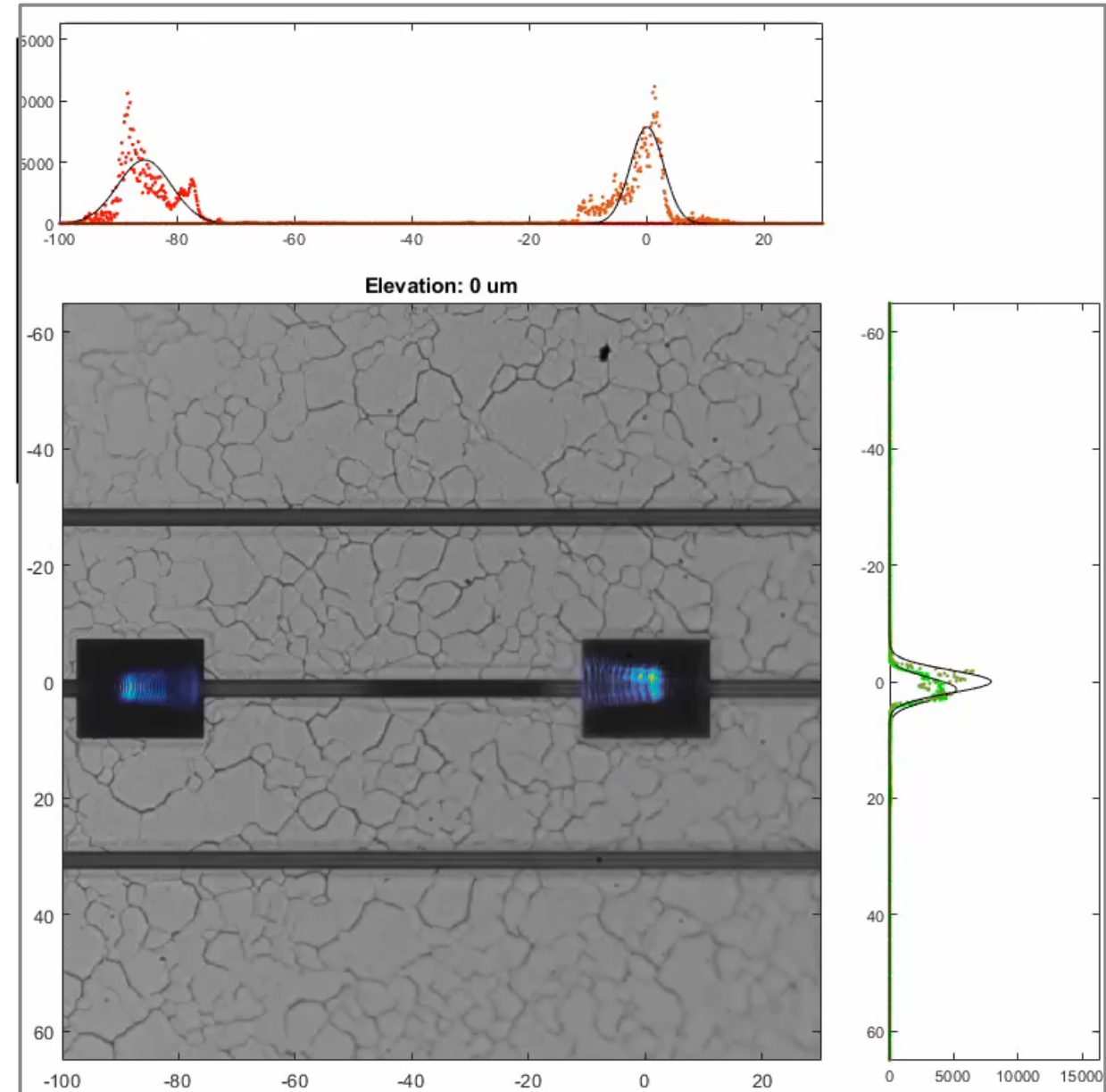
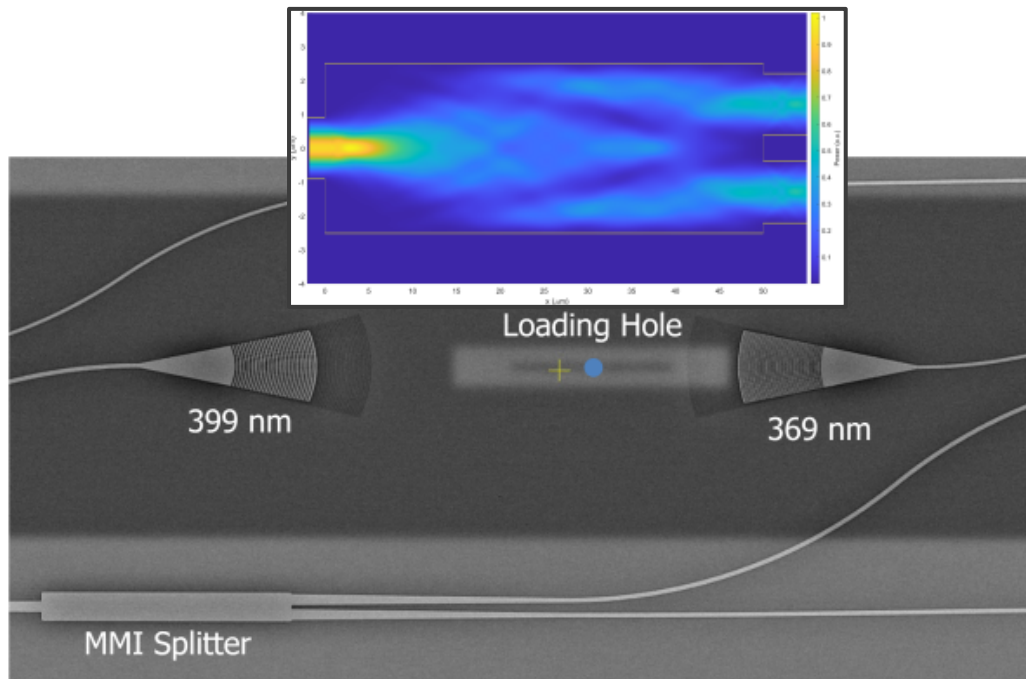
- Silicon Nitride WG material
 - VIS/NIR wavelengths
- New-ish Aluminum Oxide WG material
 - UV/VIS wavelengths
 - ~ 3 dB/cm @ 369 nm
 - Preliminary results at 355 nm: 4 dB/cm
- Angles highly accurate, < 1 μm horizontal error



Waveguides and Gratings + Ion Traps

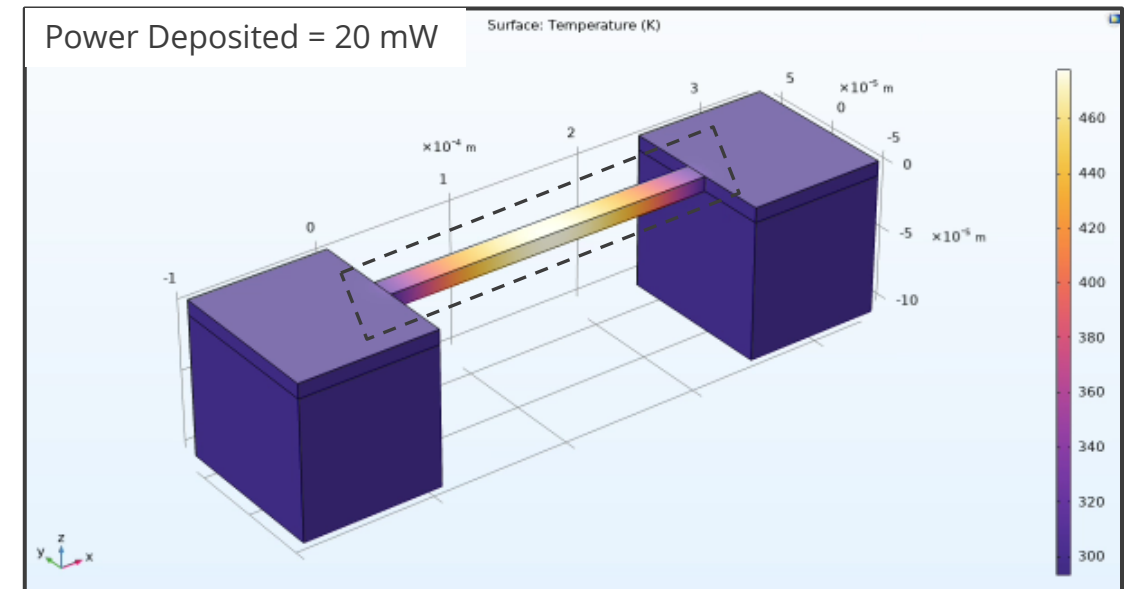
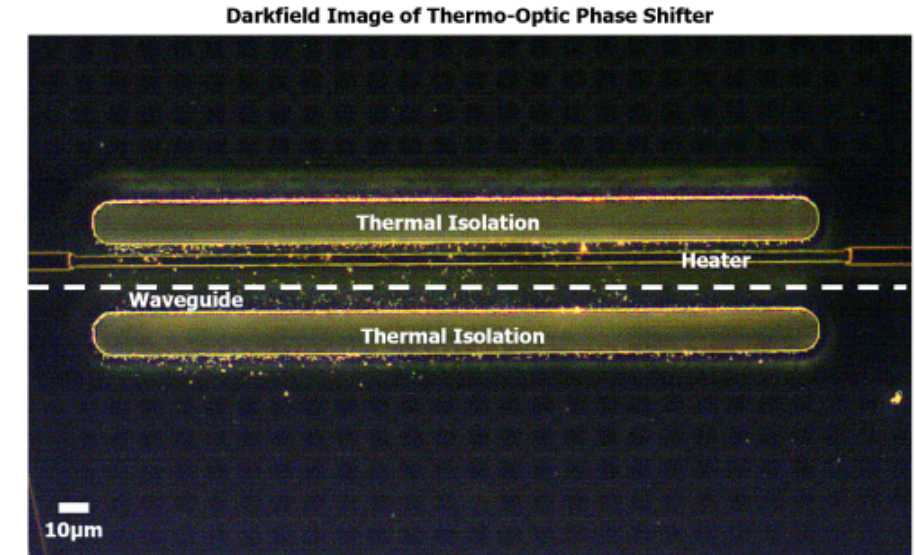
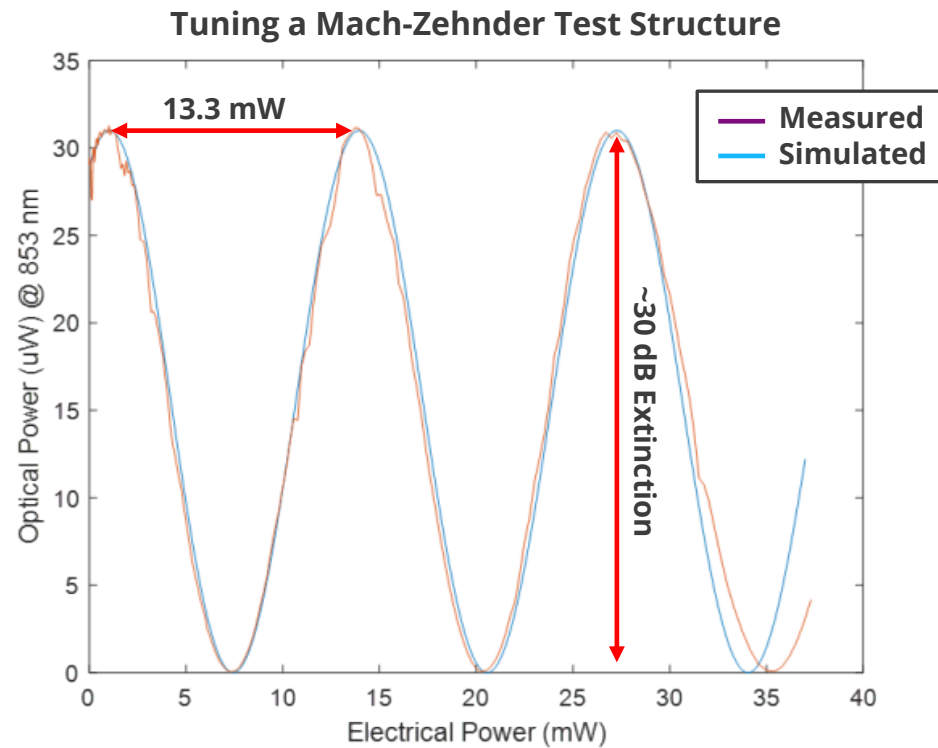
- Focusing Gratings:
 - ~ 4 to 8 μm spot sizes
- Gratings for ion loading
 - Need good overlap
 - Overlap for quantum operations
 - Doppler and Repump beams

MMI simulation



Phase Shifters

- Thermo-optic phase shifter characterized and show excellent efficiency and range
 - 6.65 mW/ π phase shift
 - $>5\pi$ total phase shift possible before damage
 - ~30 dB extinction on Mach Zehnder test structures



Waveguides + Ions Results

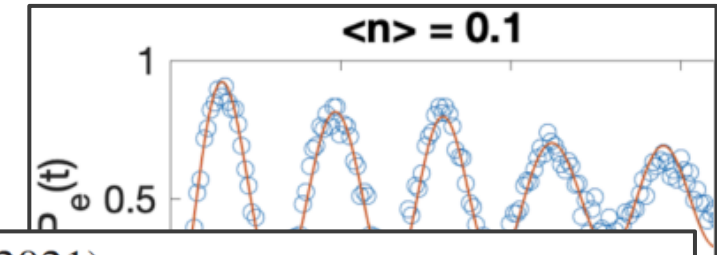


Waveguide/grating integrated trap

- L
- R
- D

Heating

- N
- N



PHYSICAL REVIEW X **11**, 041033 (2021)

Integrated Optical Addressing of a Trapped Ytterbium Ion

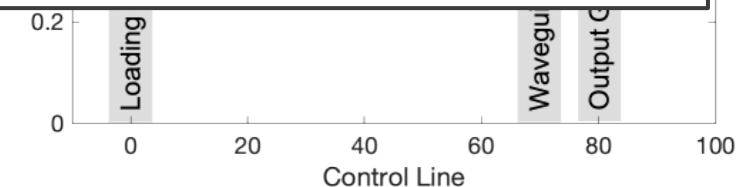
M. Ivory¹,* W. J. Setzer¹, N. Karl¹, H. McGuinness, C. DeRose, M. Blain, D. Stick¹, M. Gehl, and L. P. Parazzoli¹

Sandia National Laboratories, Albuquerque, New Mexico 87185, USA



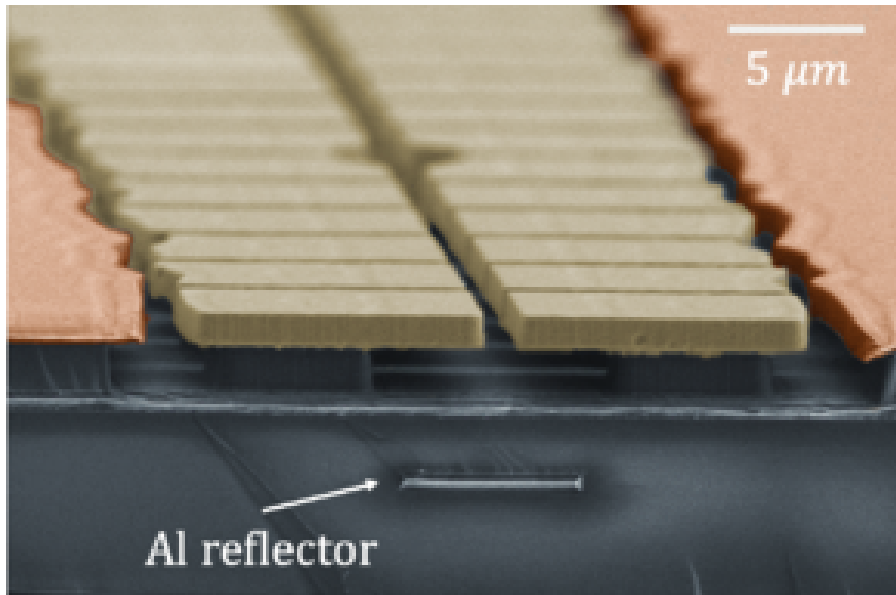
(Received 19 November 2020; revised 27 April 2021; accepted 31 August 2021; published 16 November 2021)

We report on the characterization of heating rates and photoinduced electric charging on a micro-fabricated surface ion trap with integrated waveguides. Microfabricated surface ion traps have received considerable attention as a quantum information platform due to their scalability and manufacturability. Here, we characterize the delivery of 435-nm light through waveguides and diffractive couplers to a single ytterbium ion in a compact trap. We measure an axial heating rate at room temperature of 0.78 ± 0.05 q/ms and see no increase due to the presence of the waveguide. Furthermore, the electric field due to charging of the exposed dielectric outcoupler settles under normal operation after an initial shift. The frequency instability after settling is measured to be 0.9 kHz.

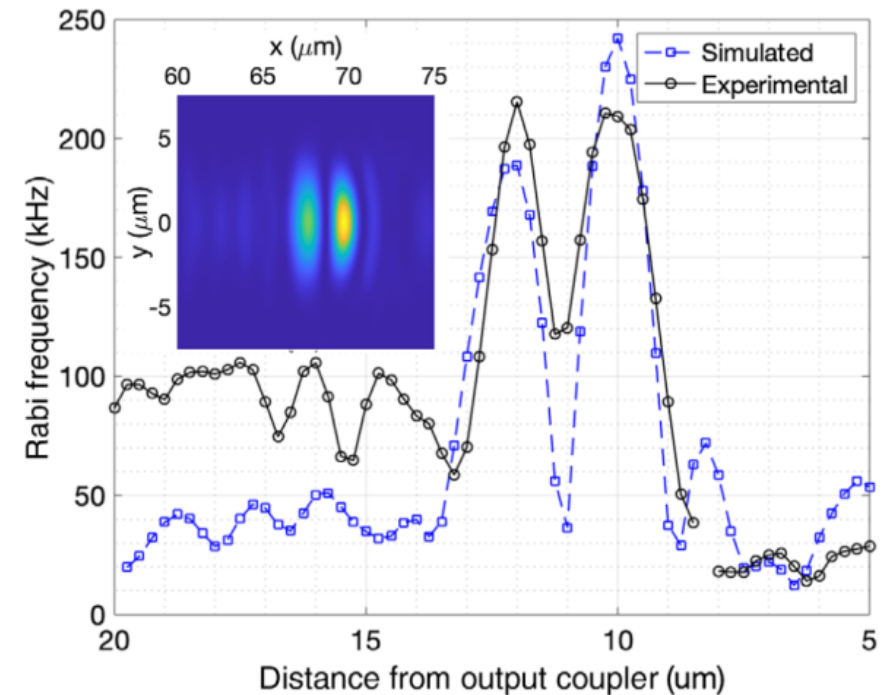
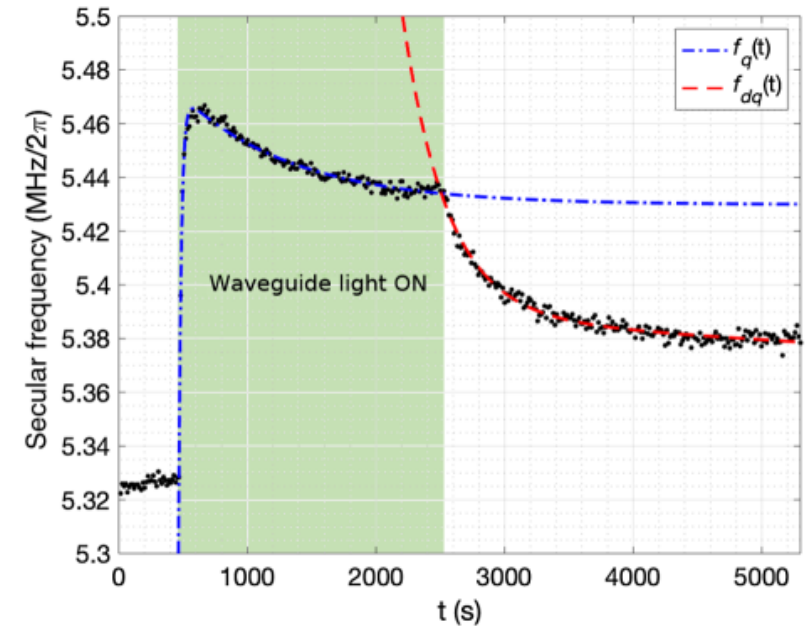


Waveguides + Ions Results 2

- Grating dielectric did have an effect
 - Significant shift of secular frequency
 - Long term drifts
 - Consistent with photoinduced charging models
- Reflector plate impact
 - Meant to redirect downward diffraction to ion
 - On the edge of fabrication resolution: double peak



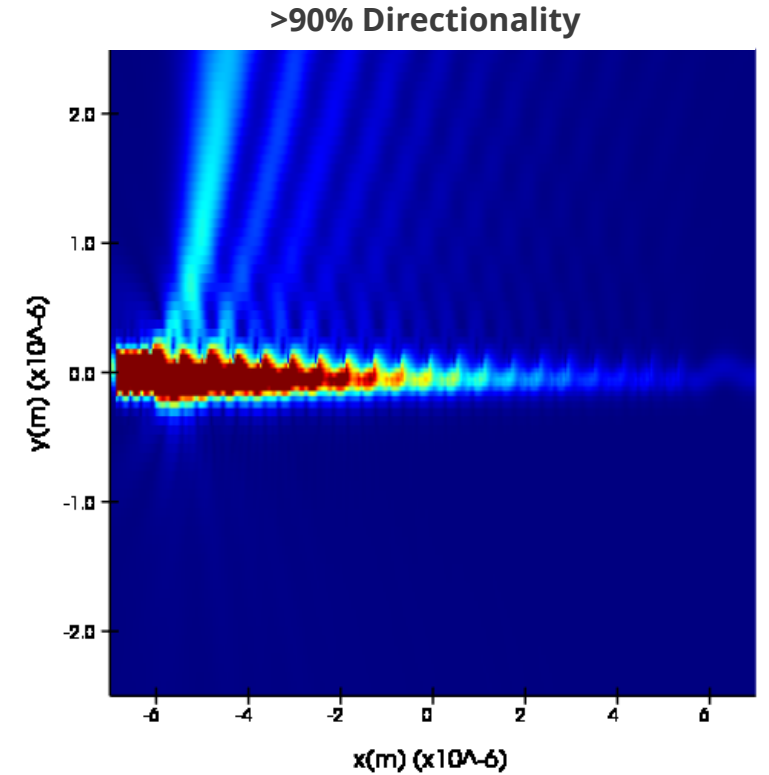
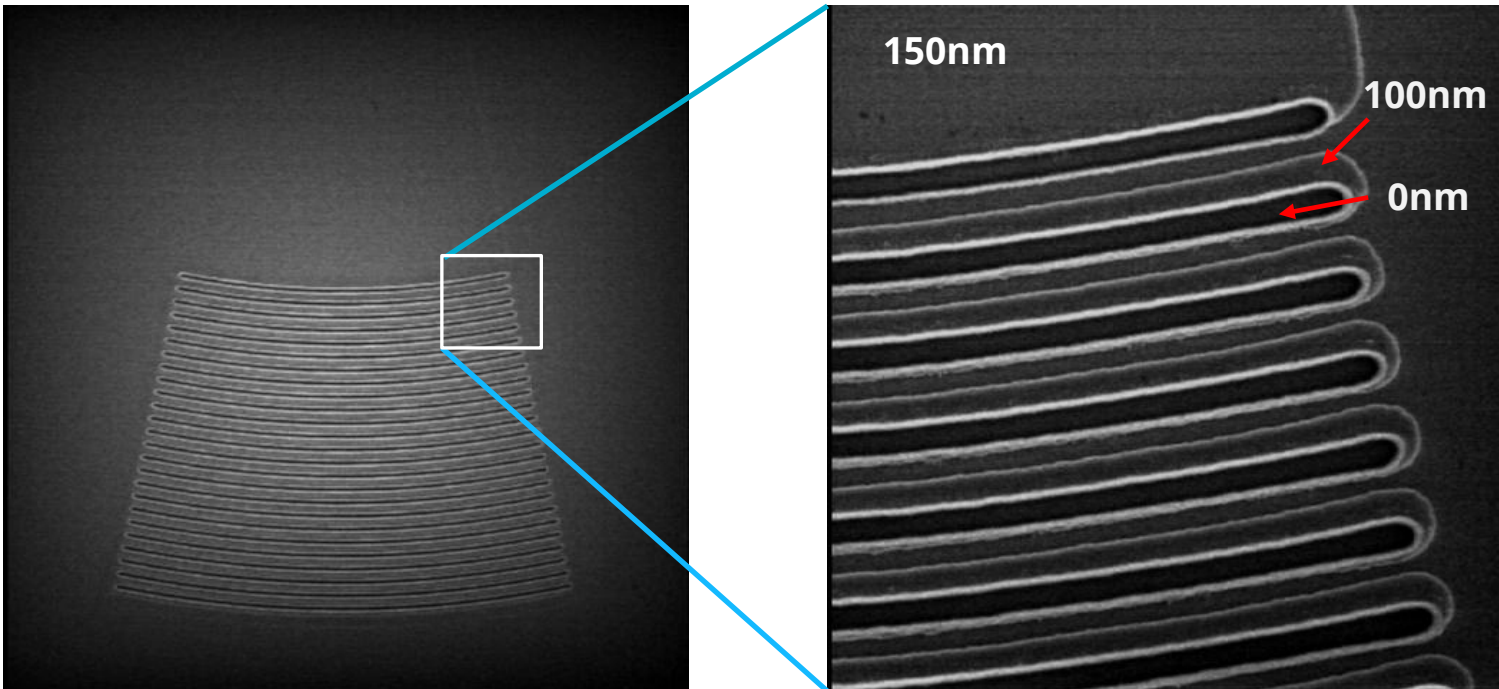
PRX 11, 041033 (2021)



Future Directions for WGs + traps



- Highly direction output gratings
 - Send most light towards the ion
 - Enabled by multi-level fabrication
 - Ridge waveguide design and polarization rotation possible
- More Traps
 - Preliminary results for ps pulsed 355 in WGs good.

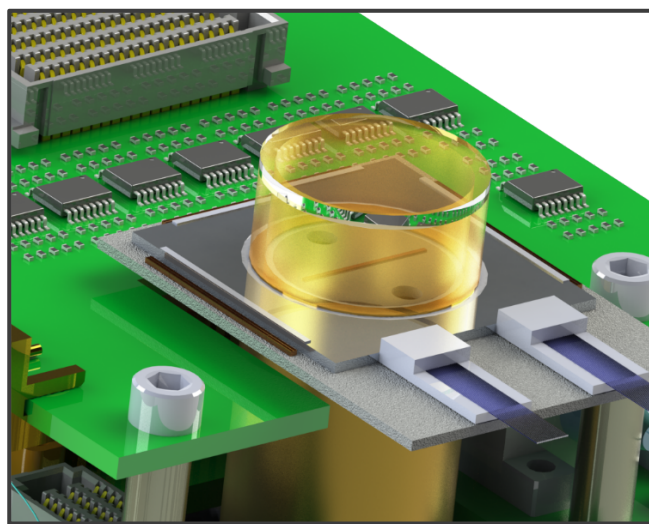
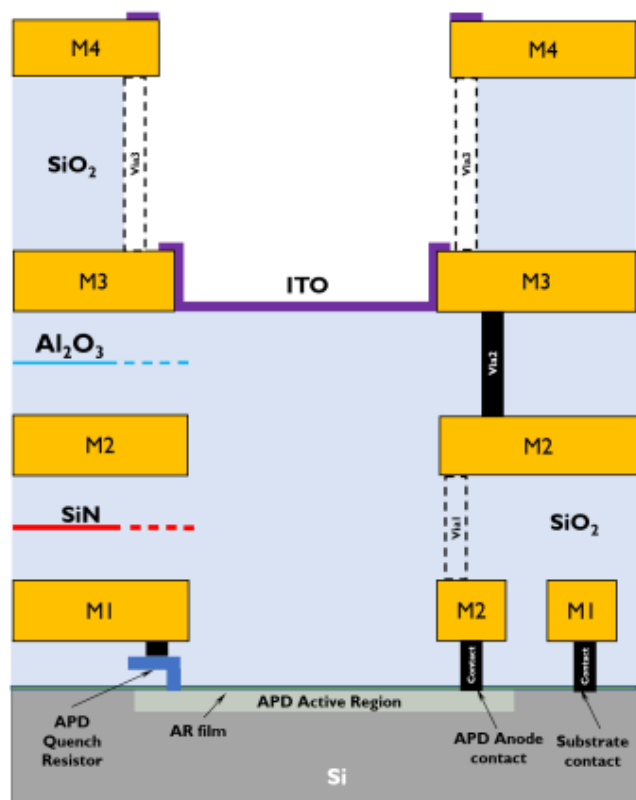
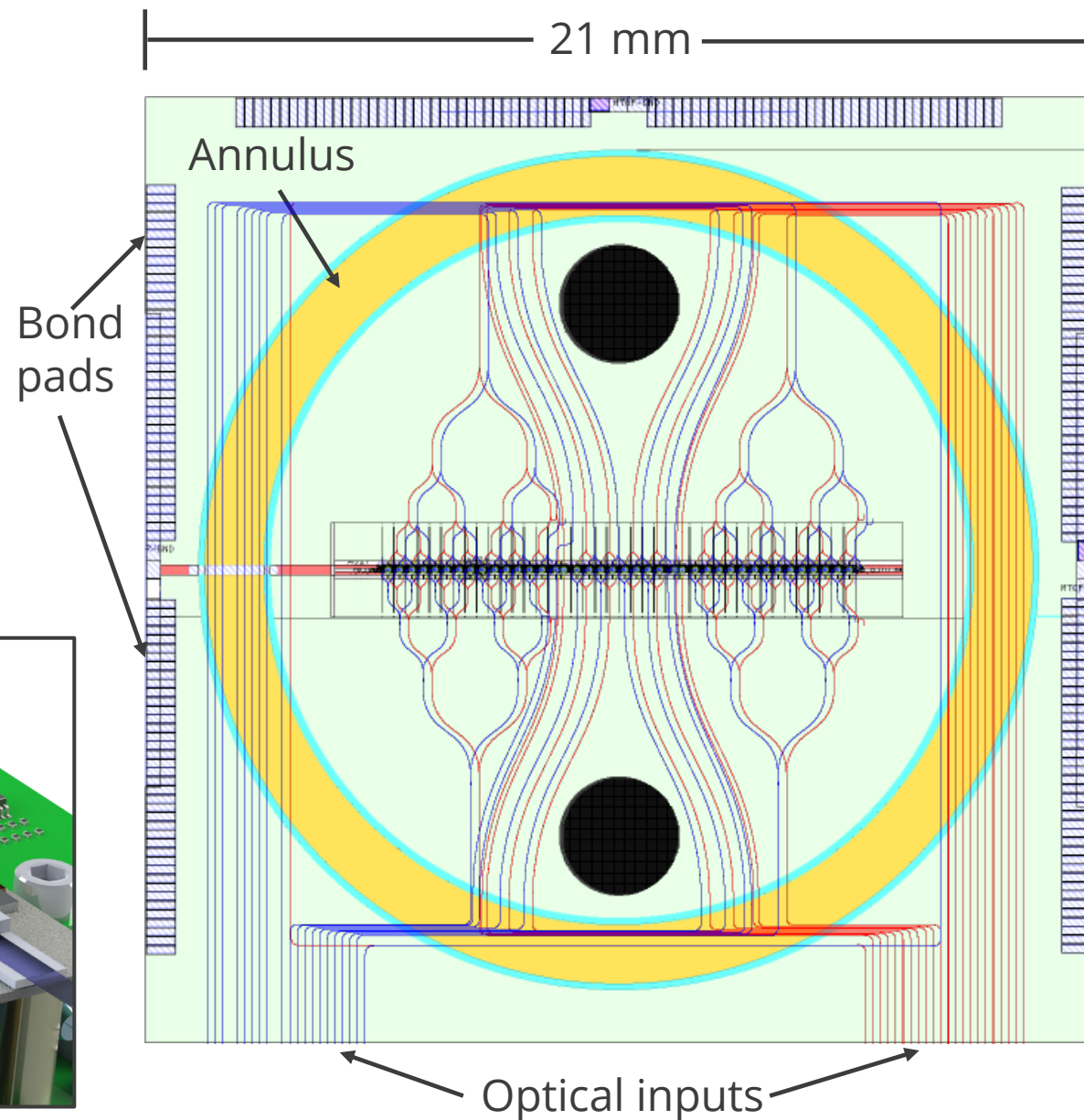


Future Directions for WGs + Traps: Fiber Attach



➤ Outside chamber v-groove/Trap attachment

- 26 UV, Visible, NIR channels
- Trap surface is part of the vacuum chamber
- 369, 399, 435, 760, 935 nm beams





Trap-Integrated Single Photon Avalanche Diodes



Single Photon Avalanche Diodes (SPADs) + Traps



➤ First demonstration of trap-integrated SPAD

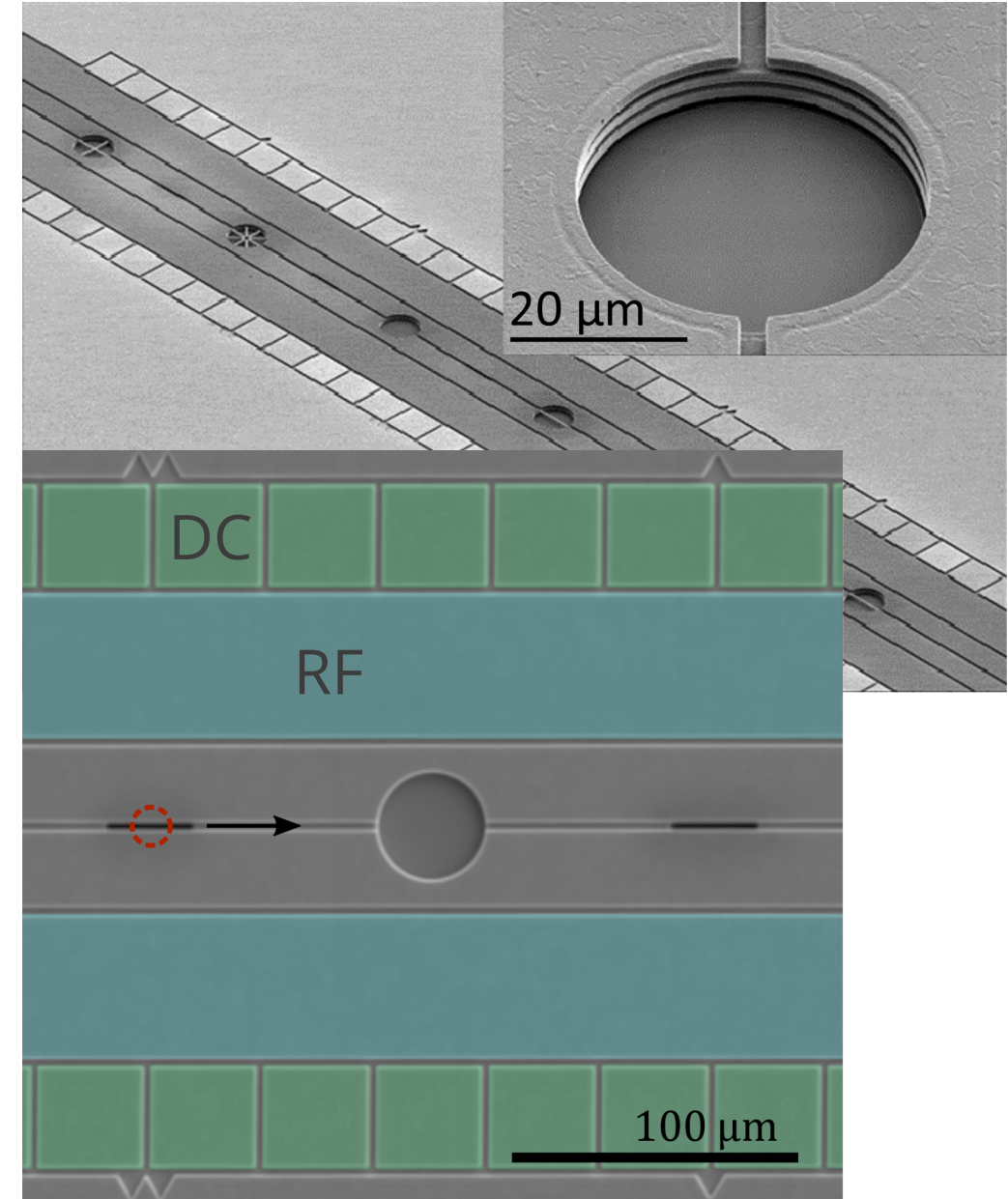
- Room temperature operation
- Average efficiency ~ 24% at 369 nm
- ~ 40 μm diameter

➤ Not problem free

- High Dark Count Rates (DCRs, ~ few kHz): defection creation?
- SPAD firing significantly disrupts ions, couldn't hold ion directly over trap.

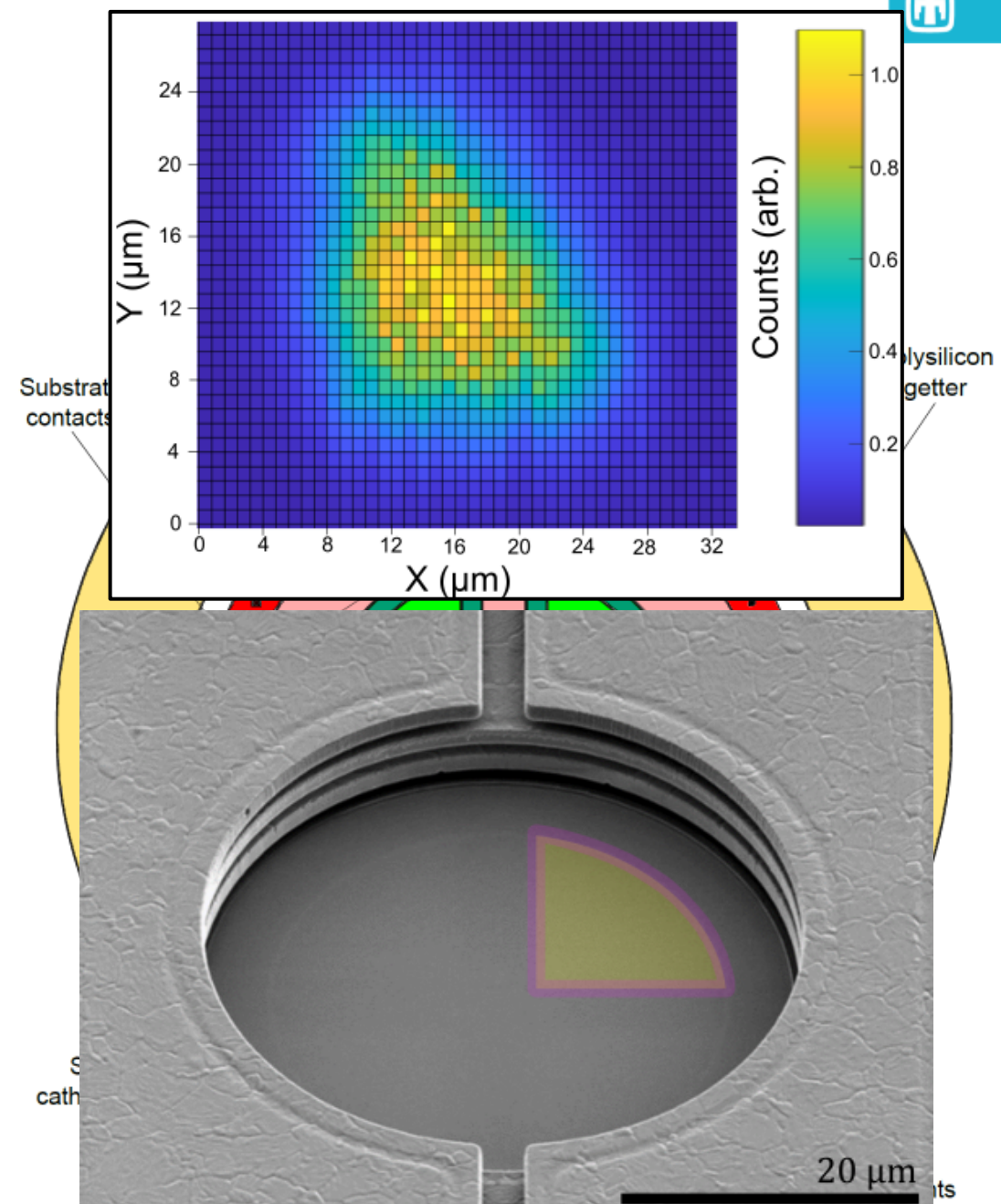
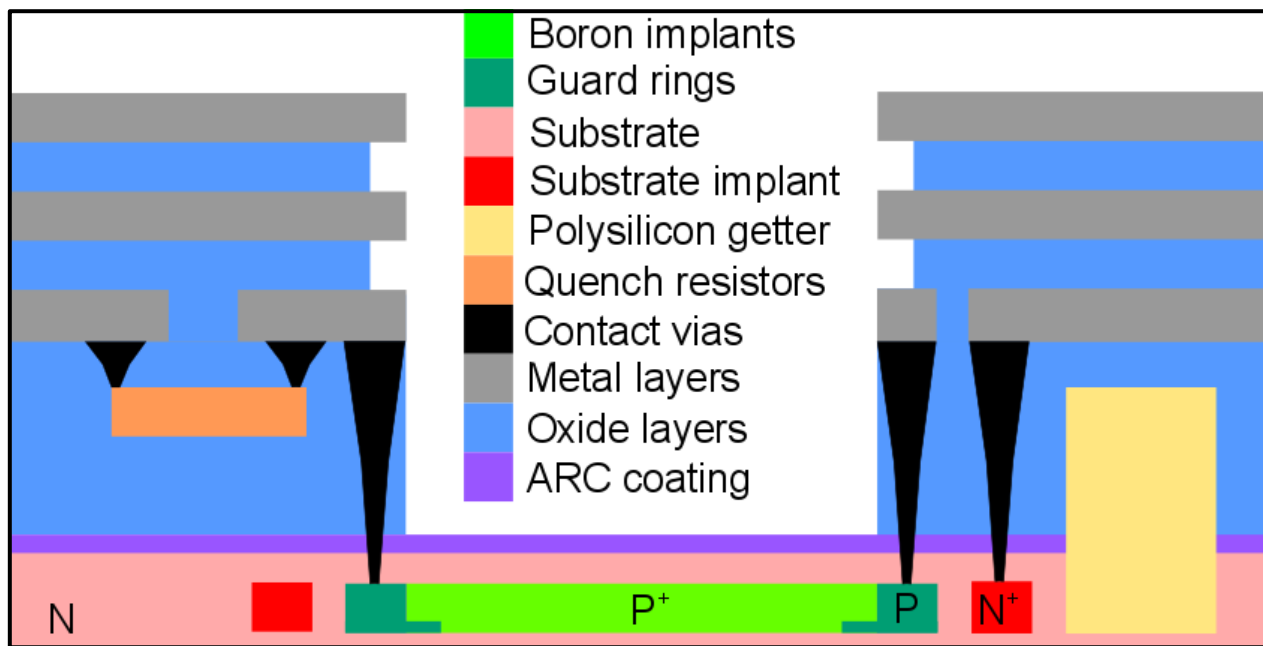


Appl. Phys. Lett. **119**, 1540222 (2021)



SPAD Composition and Design

- SPADs Monolithically integrated into surface trap
 - Process flow could be carried out in most CMOS fabs
 - ARC reduces reflections @ 369 nm from ~ 30% to ~ 10%
 - Quartered and halved active area, reduce DCR
 - Active area of quartered area ~ $60 \mu\text{m}^2$

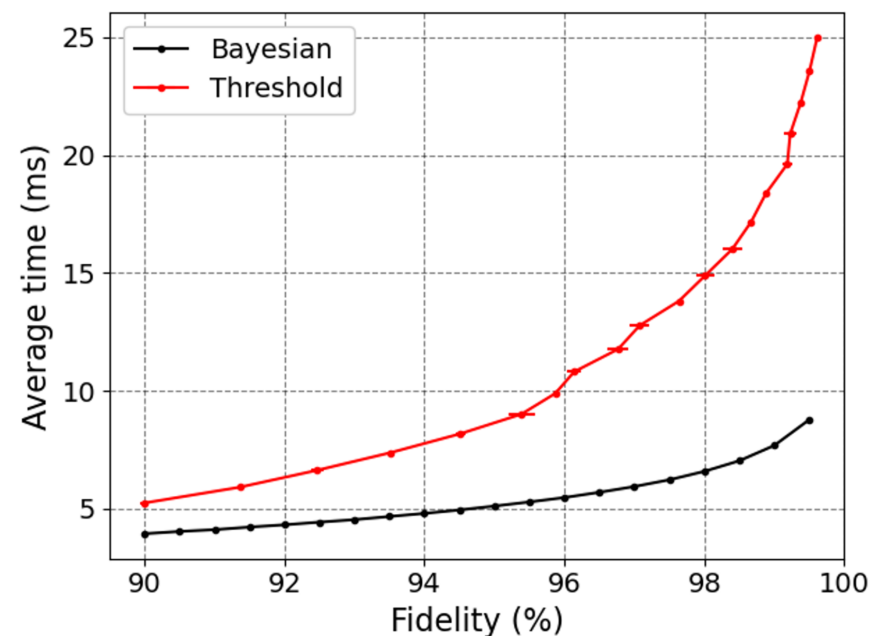
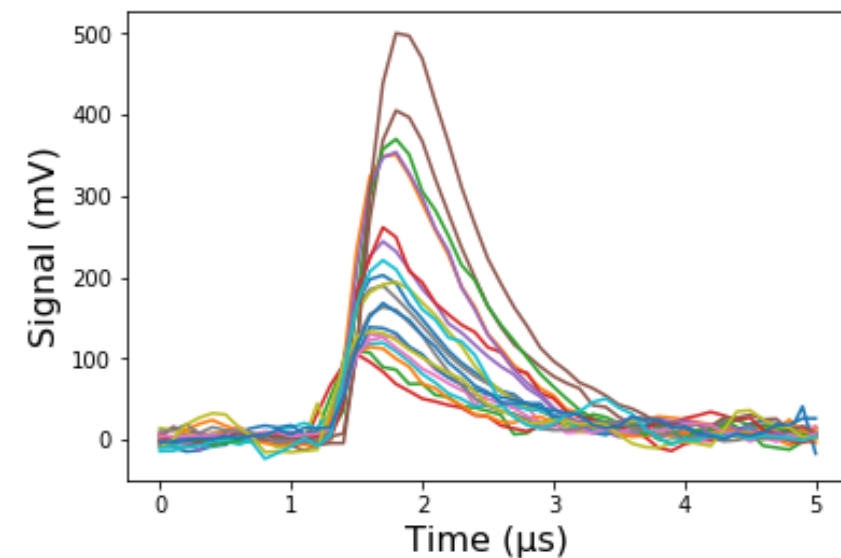
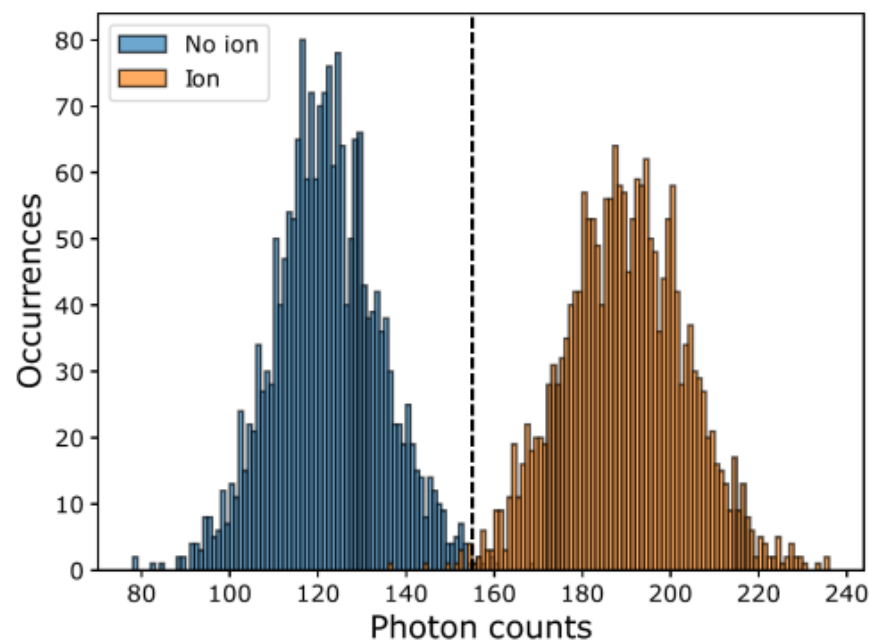


Results with Ions



- SPADs Pulses longer than wanted
 - Likely extra capacitance from long leads
- With $^{174}\text{Yb}^+$ only ion/no ion
- “Traditional” threshold vs. Bayesian detection
 - Bayesian much faster, but more complex

Source	Counts (kcps)
Ion fluorescence	4.8(1)
935 nm repump	4.0(1)
370 nm Doppler	1.4(1)
Dark counts	1.2(1)
Rf pickup	0.3(1)

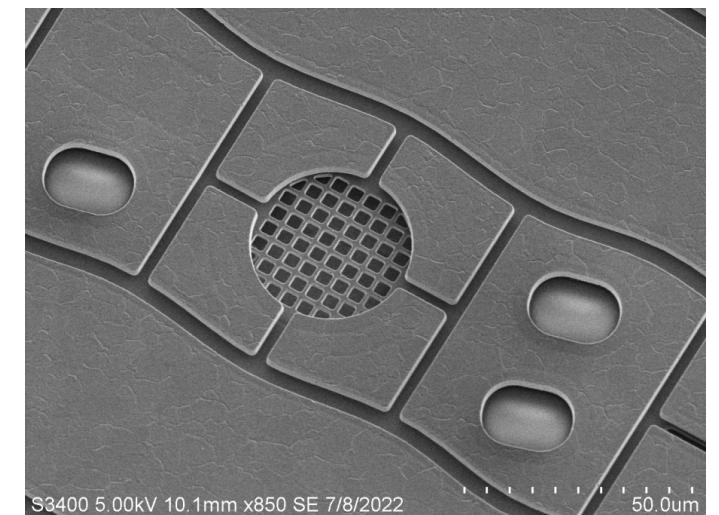
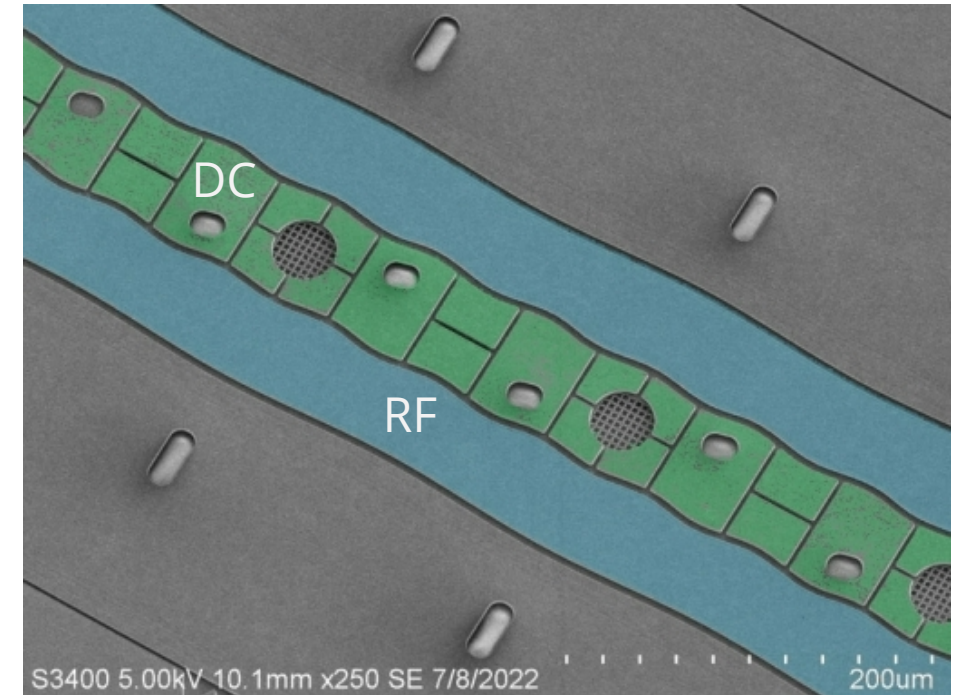
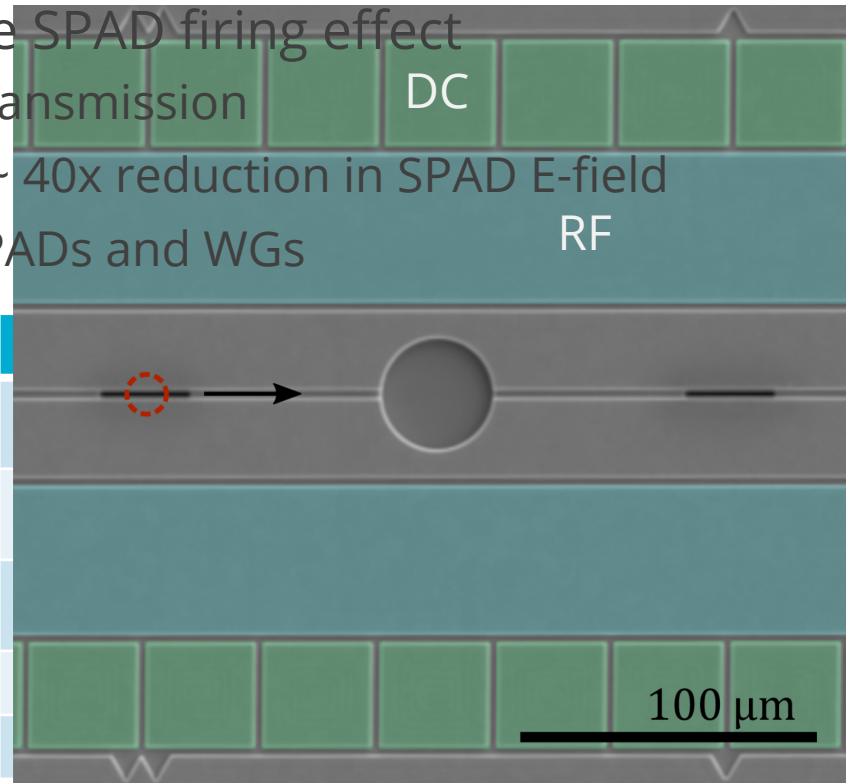


"Enhanced" SPAD/Waveguide Trap



- Version of trap with SPAD covering/waveguides
 - SPADs from previous design, new metal layers
 - "Inner" DC electrodes, much higher trap depth
 - Easier to transport over gratings
 - SPADs or WGs, not SPADs + WGs
- Metal mesh to reduce SPAD firing effect
 - Estimated ~ 56% transmission
 - Simulations show ~ 40x reduction in SPAD E-field
 - ITO in future for SPADs and WGs

Source
Ion fluorescence
935 nm repump
370 nm Doppler
Dark counts
Rf pickup



Future Directions: Final Trap!

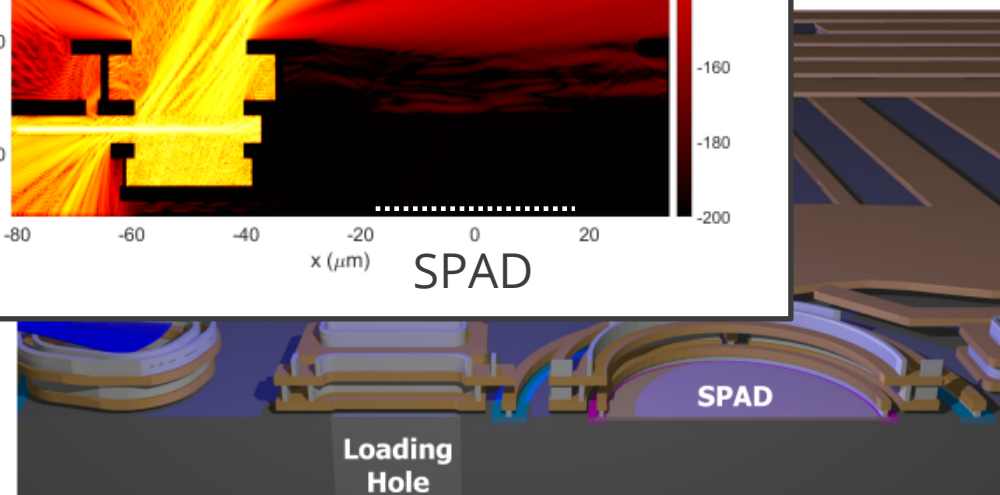
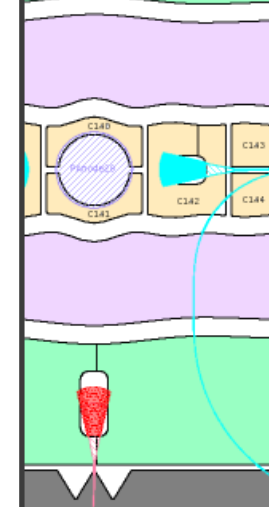
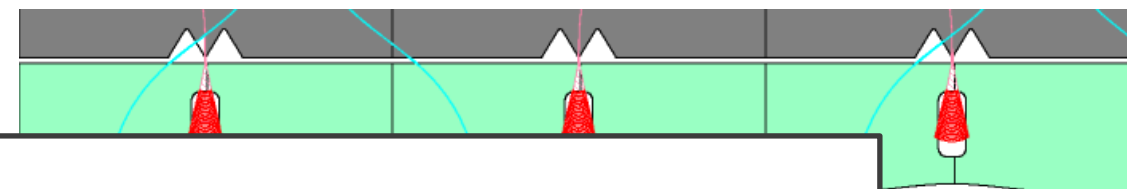
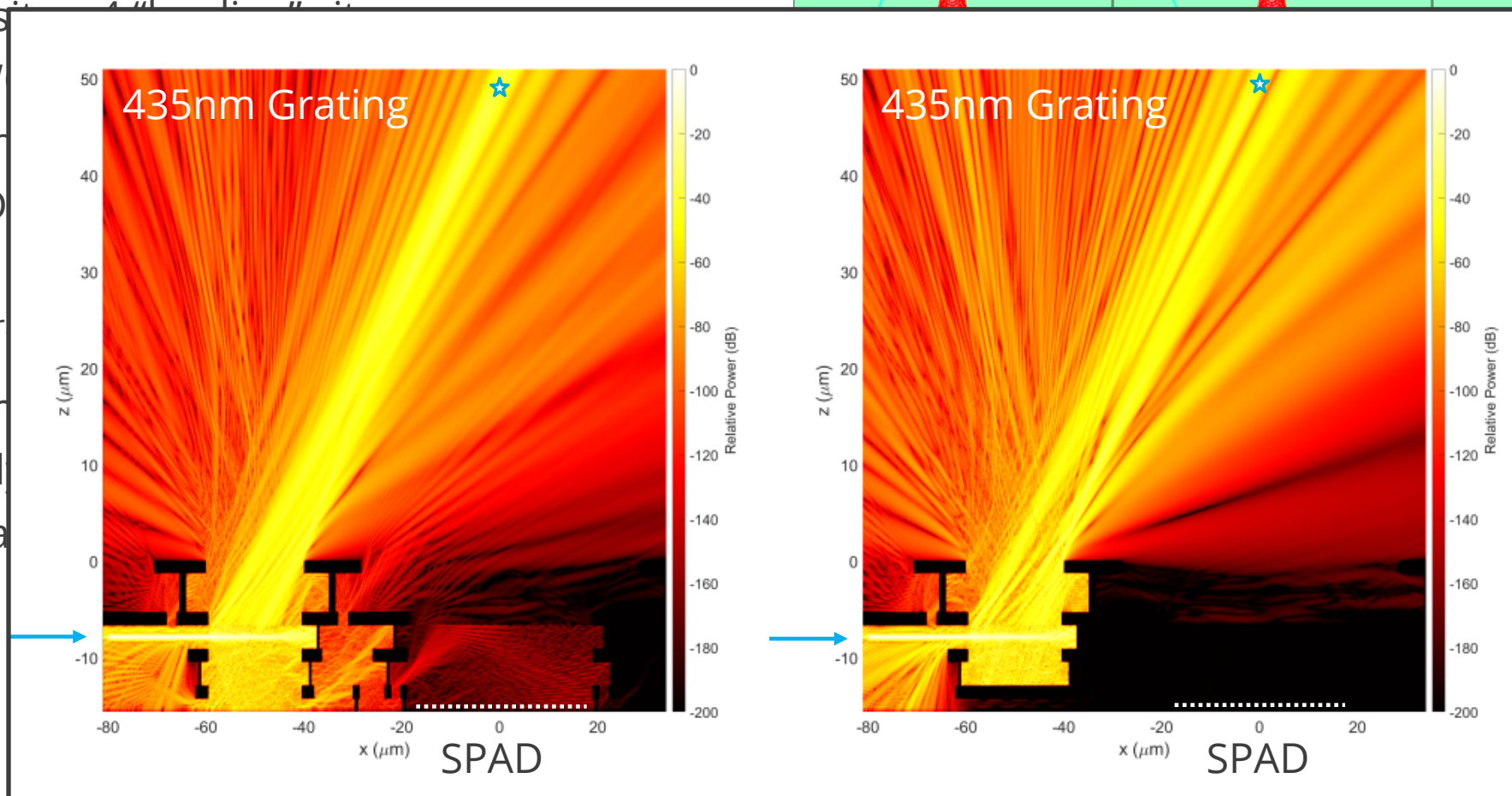


Final trap near completion

- 32 "clock" s
- SPADs + W
- ITO coverin
- "Full" SPAD
- New SPAD
- Initial DCR r

Baffles for sim

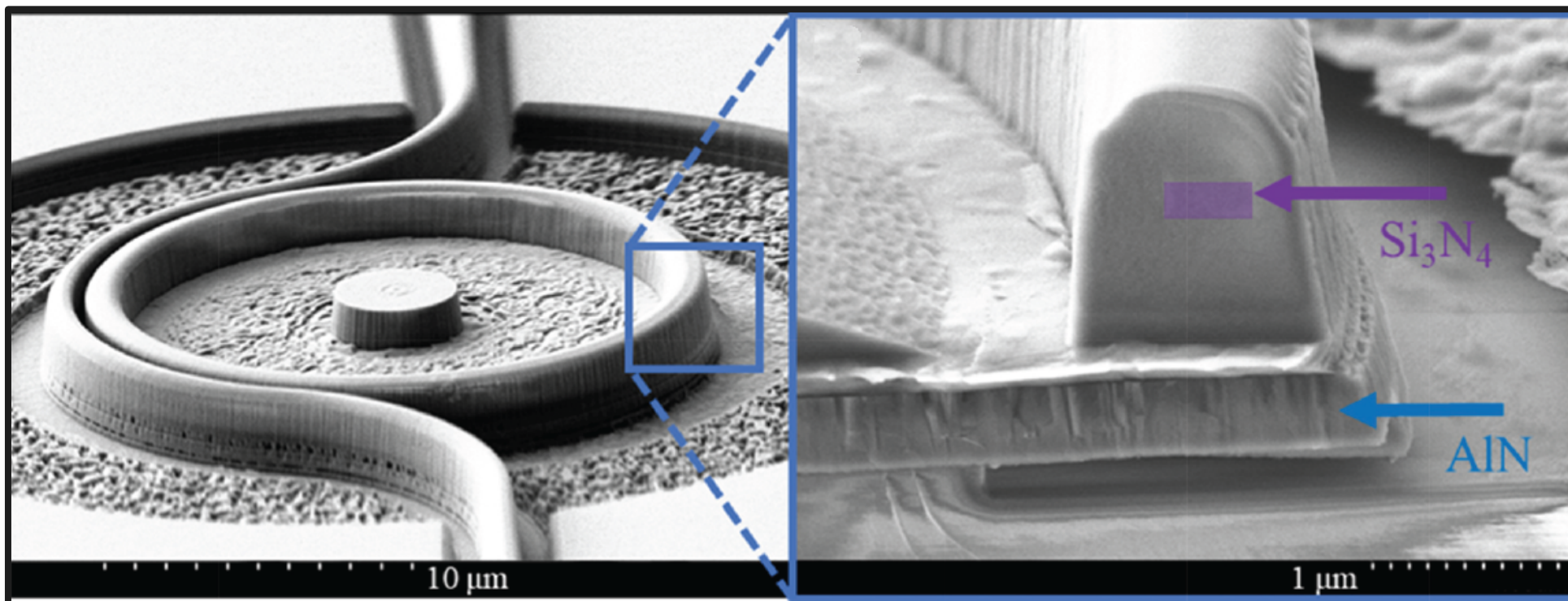
- Significantl
- Affects bea





Traps and Modulators

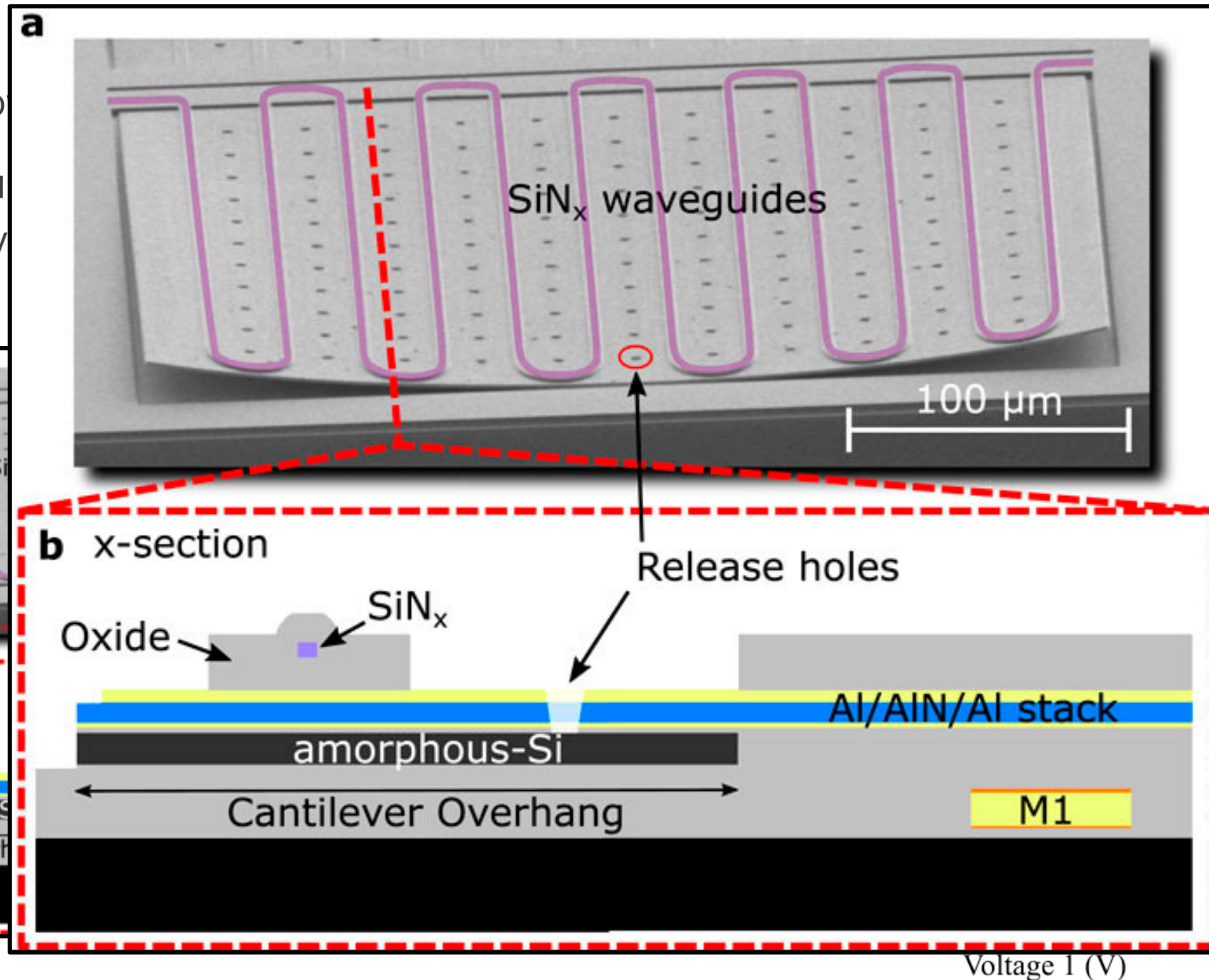
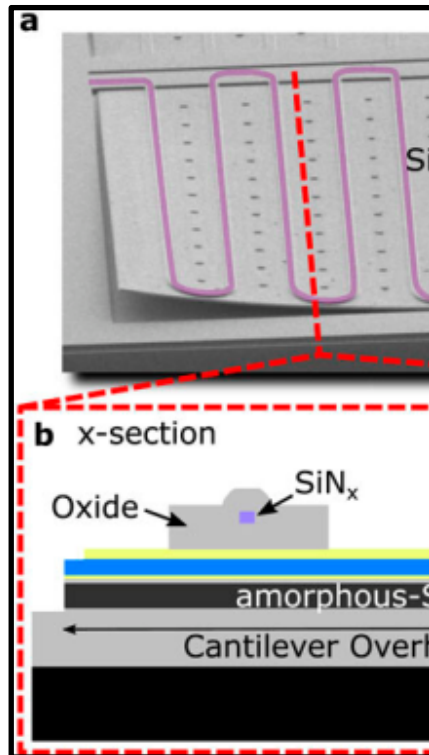




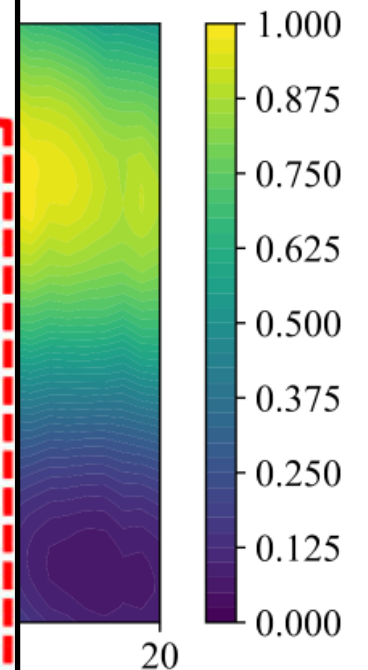
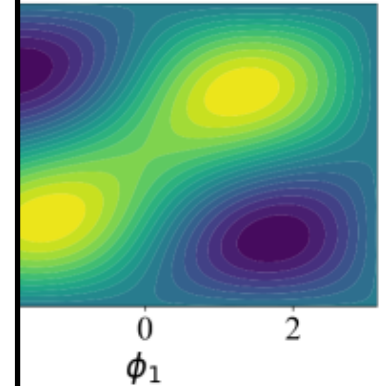
General Performance Characteristics



- SiNx waveguides on
 - Release holes allow
- Splitting ratio of couplers
 - Observed roughly



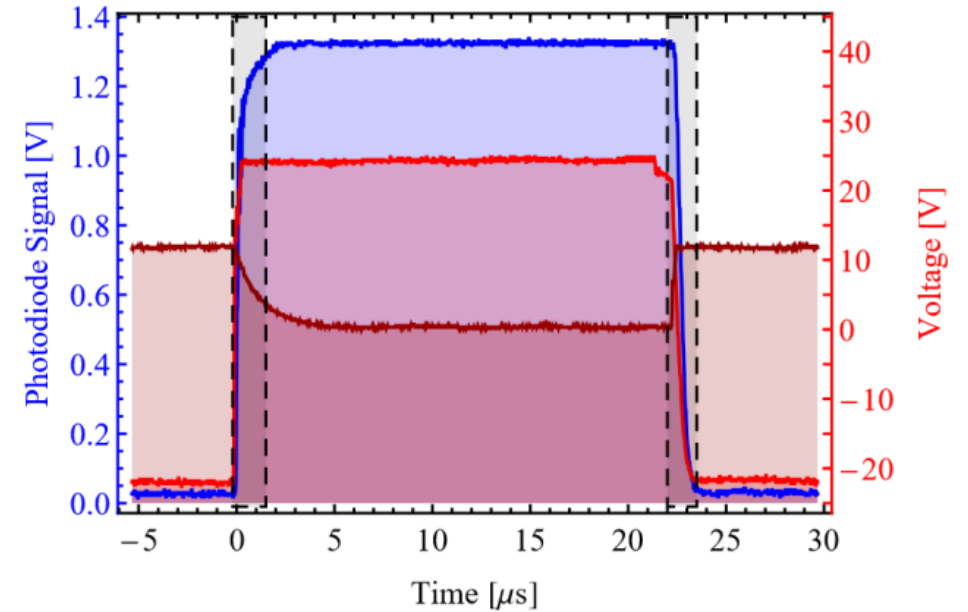
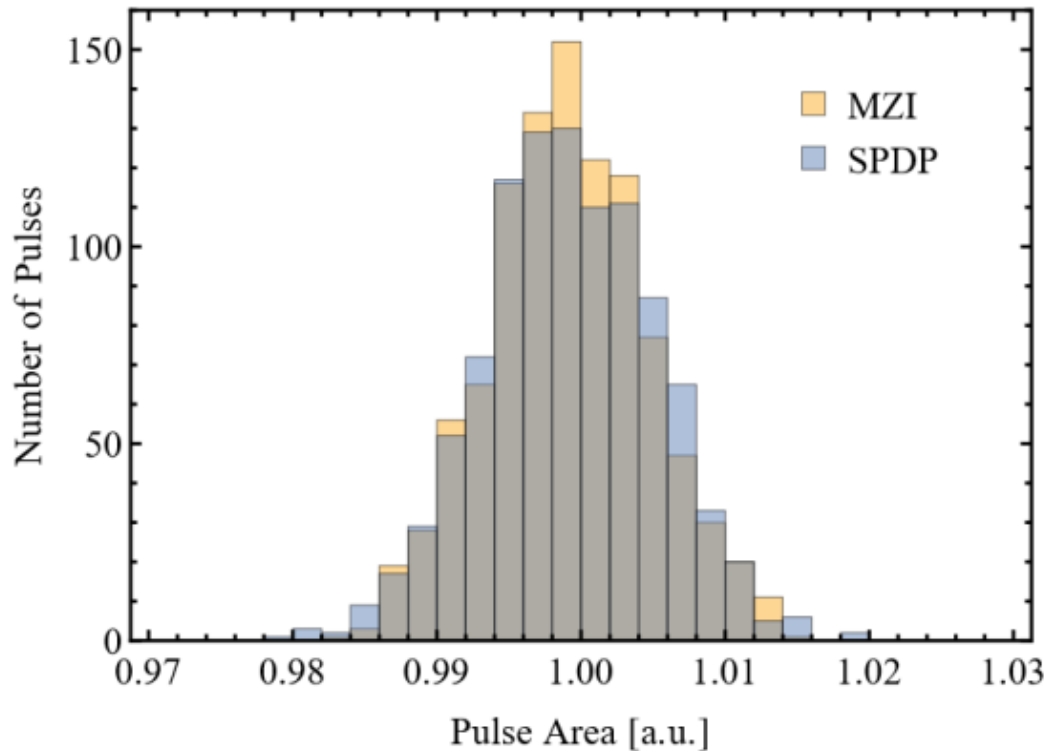
50/40 Splitters



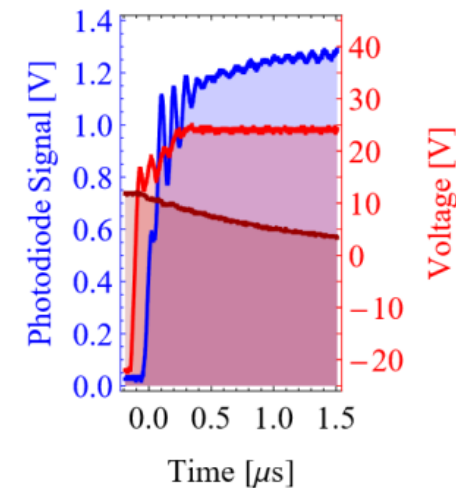
Pulse Timings and Stability



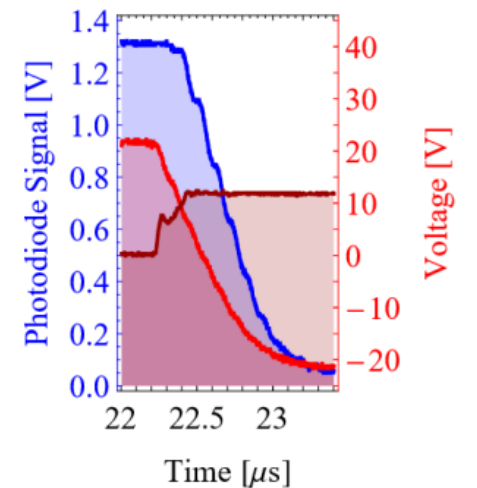
- Compare MZIs to “traditional” AOM switch
 - Single-pass/Double Pass AOMs vs. double MZIs
 - Imperfect electronic switching, but long-ish pulses
 - Integrated pulse intensity similar, detection electronics limited?



(a)



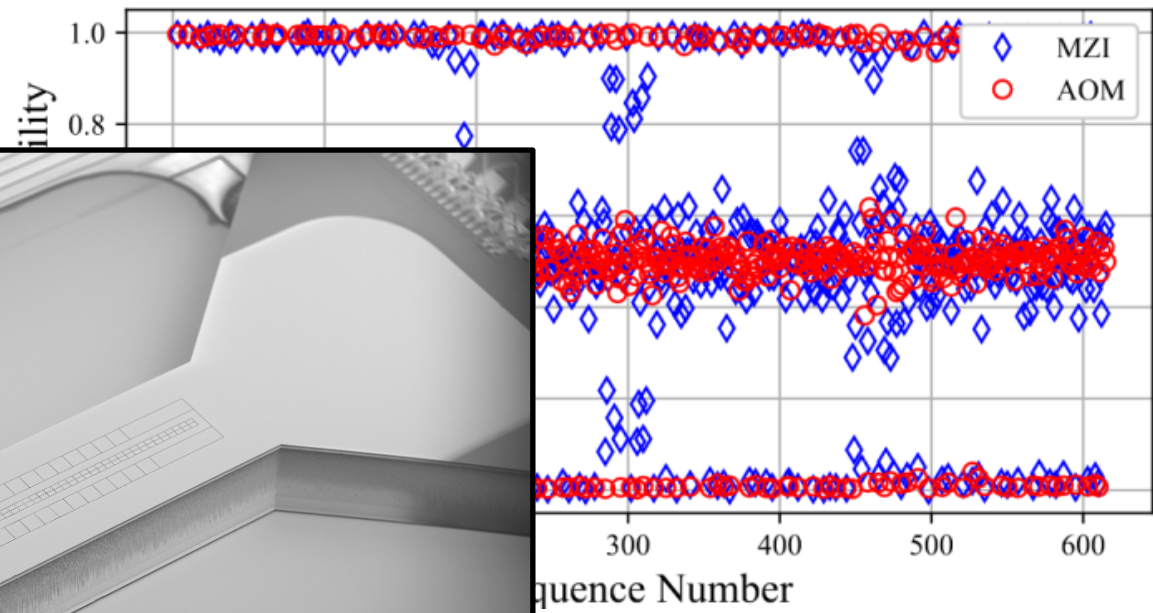
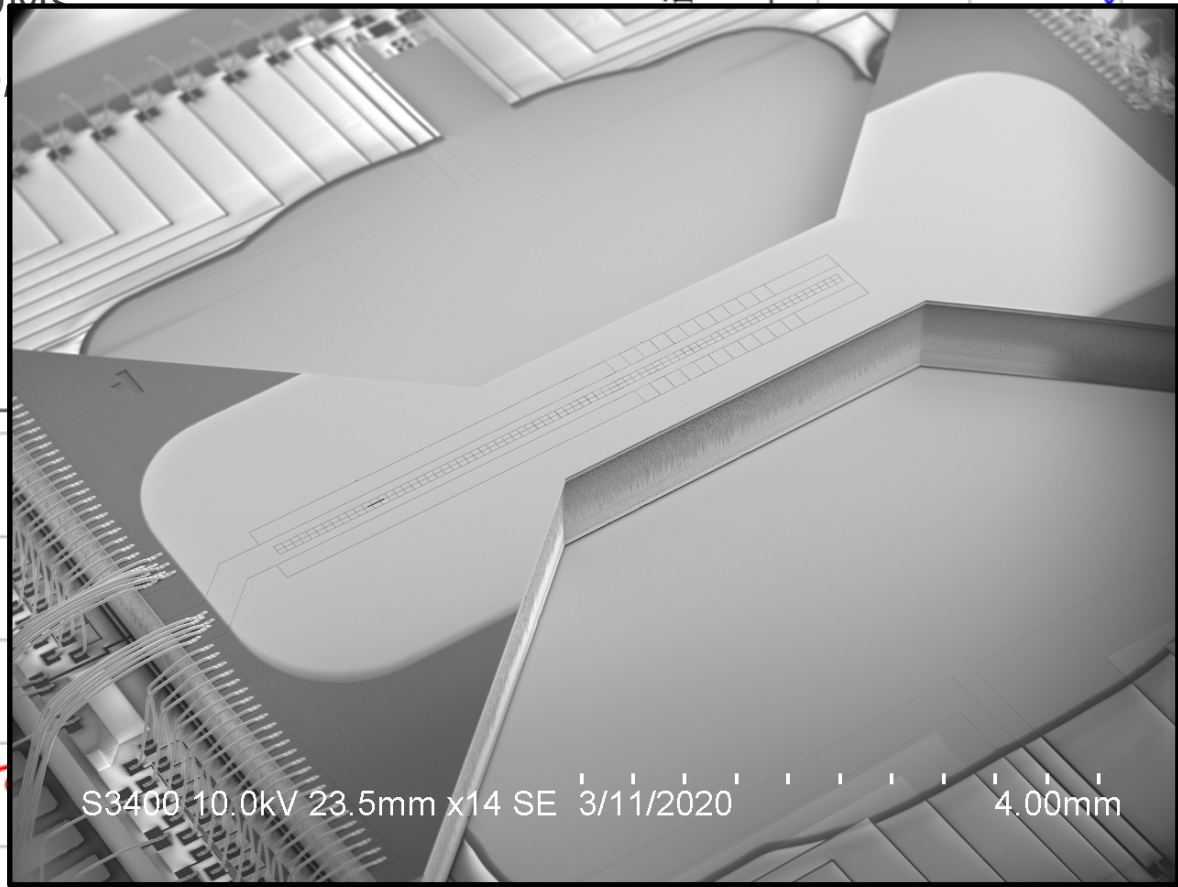
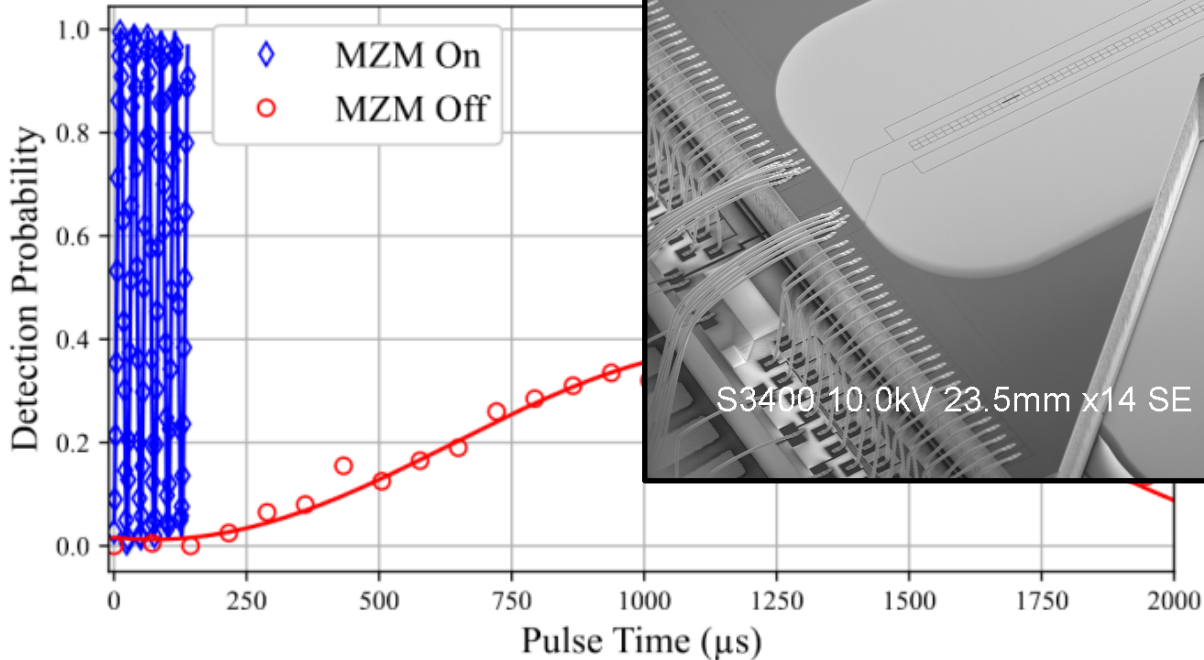
(b)



(c)

Modulators + Ions

- MZI switch inline with $^{40}\text{Ca}^+$ quad. beam (729 nm)
 - Rabi flops similar to AOMs
 - Extinction ratio ~ 38 dB
 - GST results: Somewhat
 - Identity gate the worst:



Process infidelity ($\times 10^{-3}$) (X/Y/I)		
2.6 \pm X	2.4 \pm X	2.6 \pm X
1.6 \pm X	1.5 \pm X	0.7 \pm X
0.7 \pm X	1.0 \pm X	0.1 \pm X
Diamond norm ($\times 10^{-2}$) (X/Y/I)		
MZI, input	1.5 \pm X	1.4 \pm X / 4.7 \pm X
AOM, input	2.5 \pm X	2.3 \pm X / 0.3 \pm X
AOM, output	0.5 \pm X	0.5 \pm X / 0.7 \pm X

Role the Credits

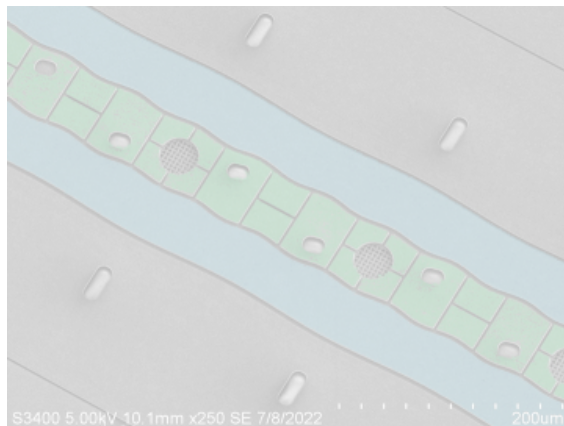
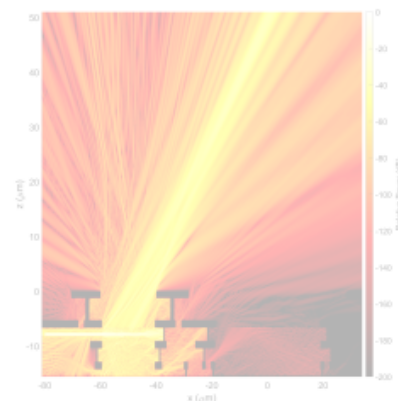
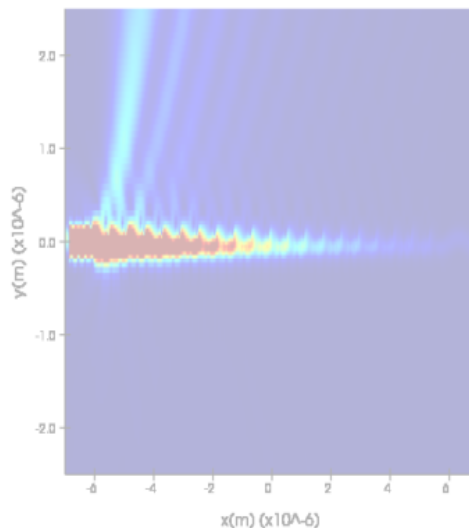
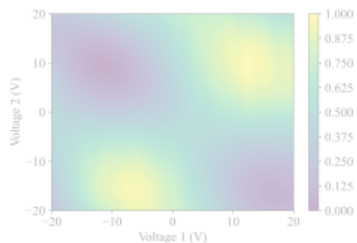
Thanks to:



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Megan Ivory
Ray Haltli
Justin Schultz

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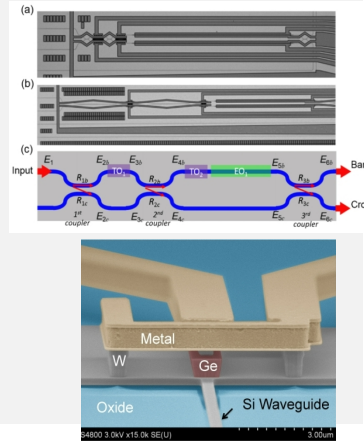
**Postdoc Positions
Available !**

Contact: Hayden McGuinness
hmcgui@sandia.gov



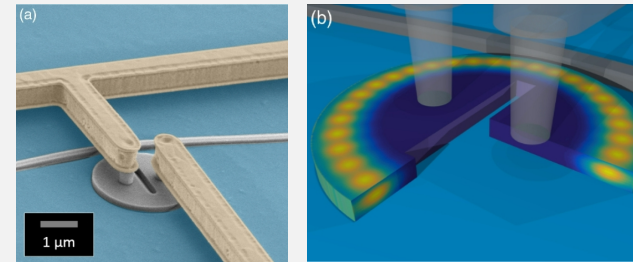
Integrated photonics for quantum communications

Sandia's silicon, III-V, alumina, lithium niobate heterogeneously integrated photonic platforms: compact microsystems for telecom and visible wavelengths



Cryogenic optical interconnects

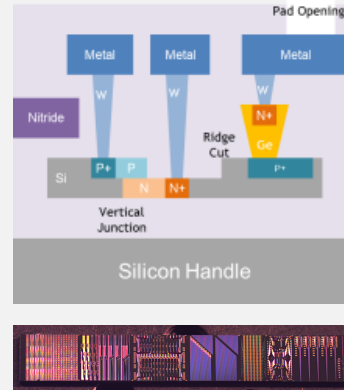
High-speed low-power resonant modulator operating at cryogenic temperatures (≤ 4 K)



Optica 4,
374-382 (2017)

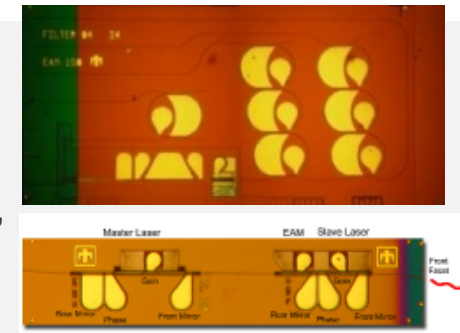
Silicon photonics integrated circuits

- Leverage CMOS (200 mm SOI)
- 22 passive devices, 20 active devices, design guide and library
- **MPW runs available**, up to passive+active+Ge devices



III-V photonic integrated circuits (PICs)

- InP, GaAs, GaN
- Elements: Waveguides, lasers, amplifiers, modulators, detectors, phase shifters
- **MPW runs available**



More information on photonics MPW opportunities:

- National Security Photonics Center: sandia.gov/mesa/nspc
- Contact photonics@sandia.gov

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DiVincenzo Criteria and Trapped Ions



- 1) A scalable physical system with well-characterized qubit : ? / YES
- 2) The ability to initialize the state of the qubits to a simple fiducial state: YES
- 3) Long relevant decoherence times : ? / YES
- 4) A "universal" set of quantum gates : YES
- 5) A qubit-specific measurement capability: YES